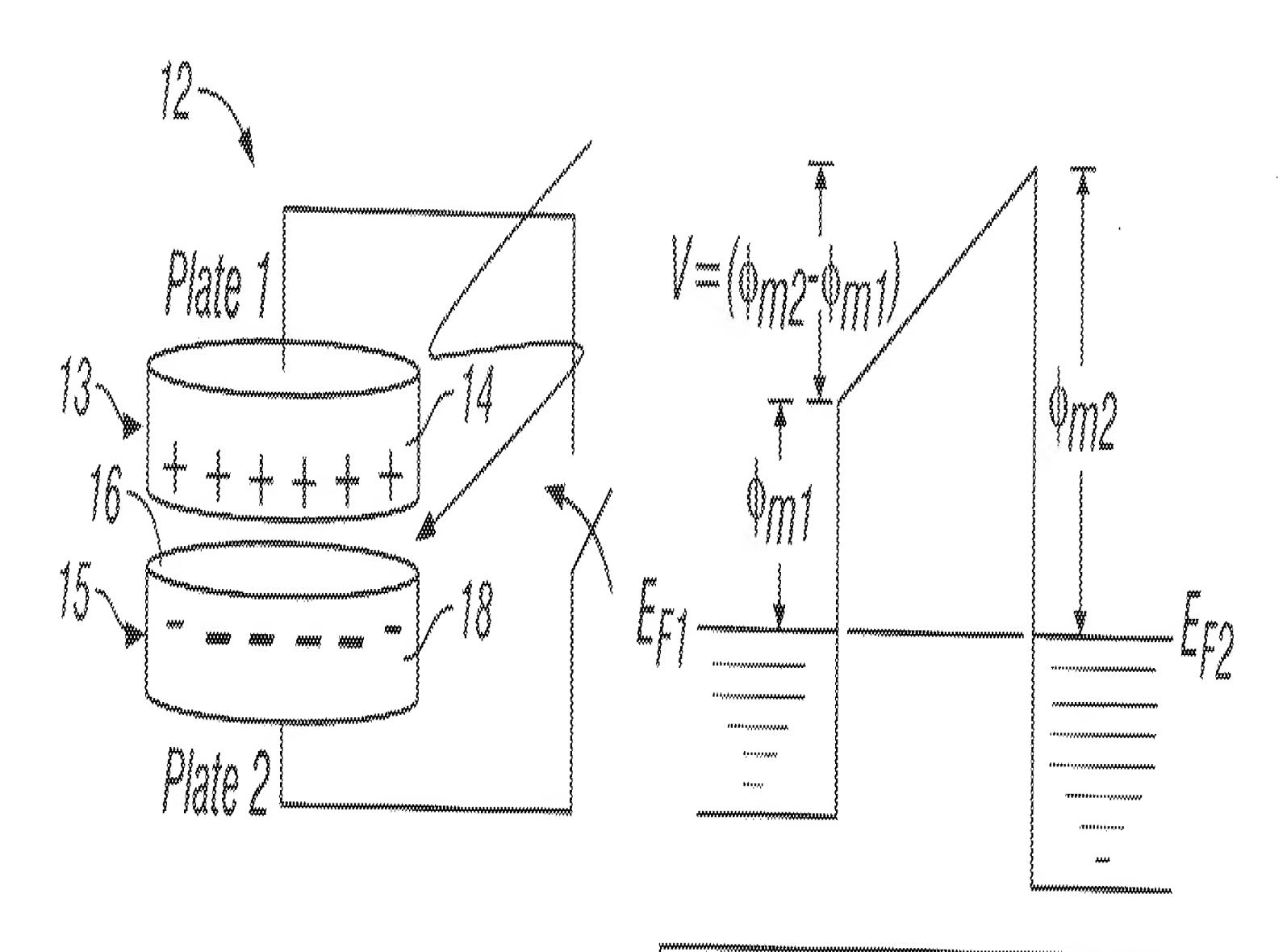


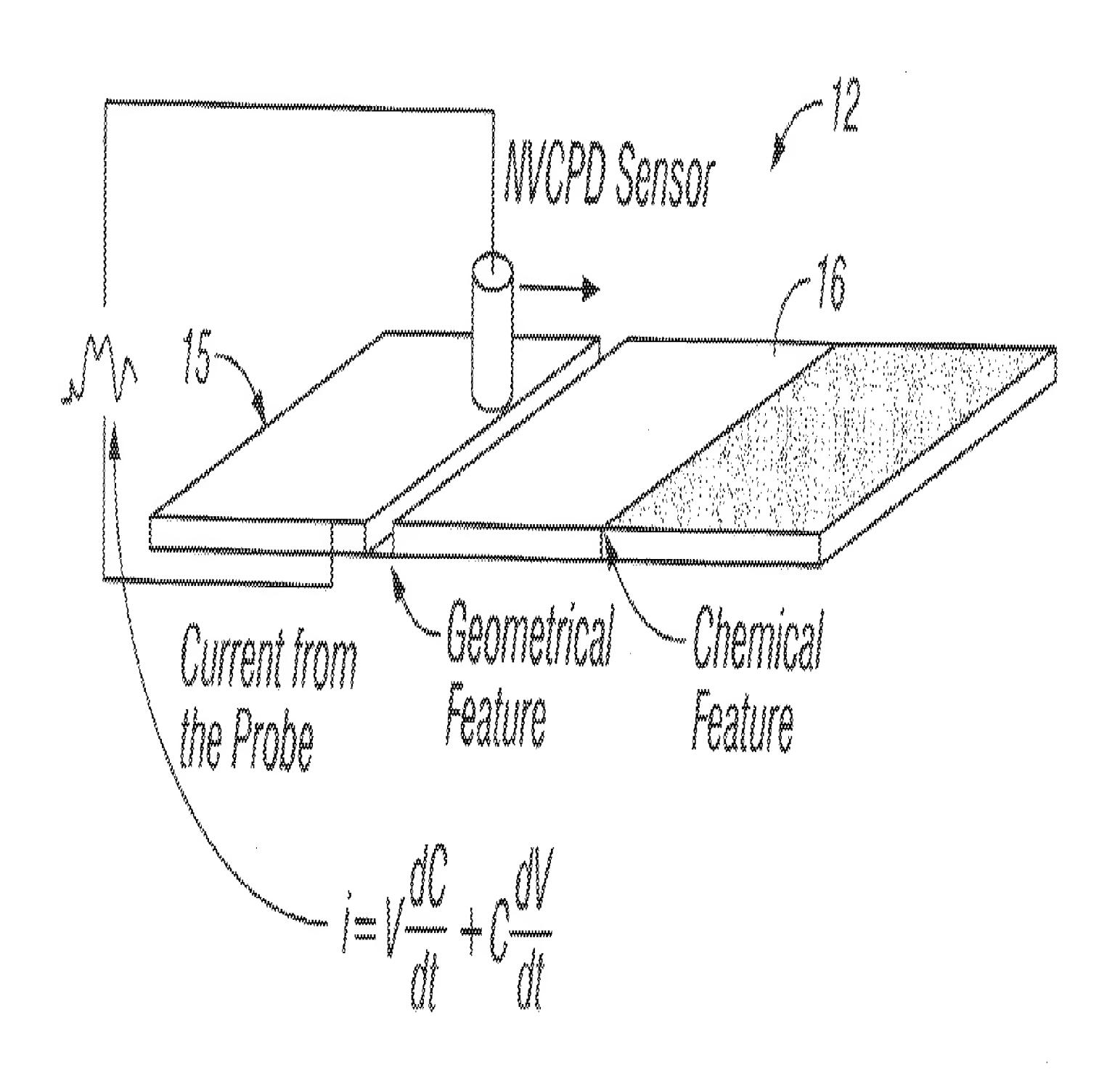
FIG. 1



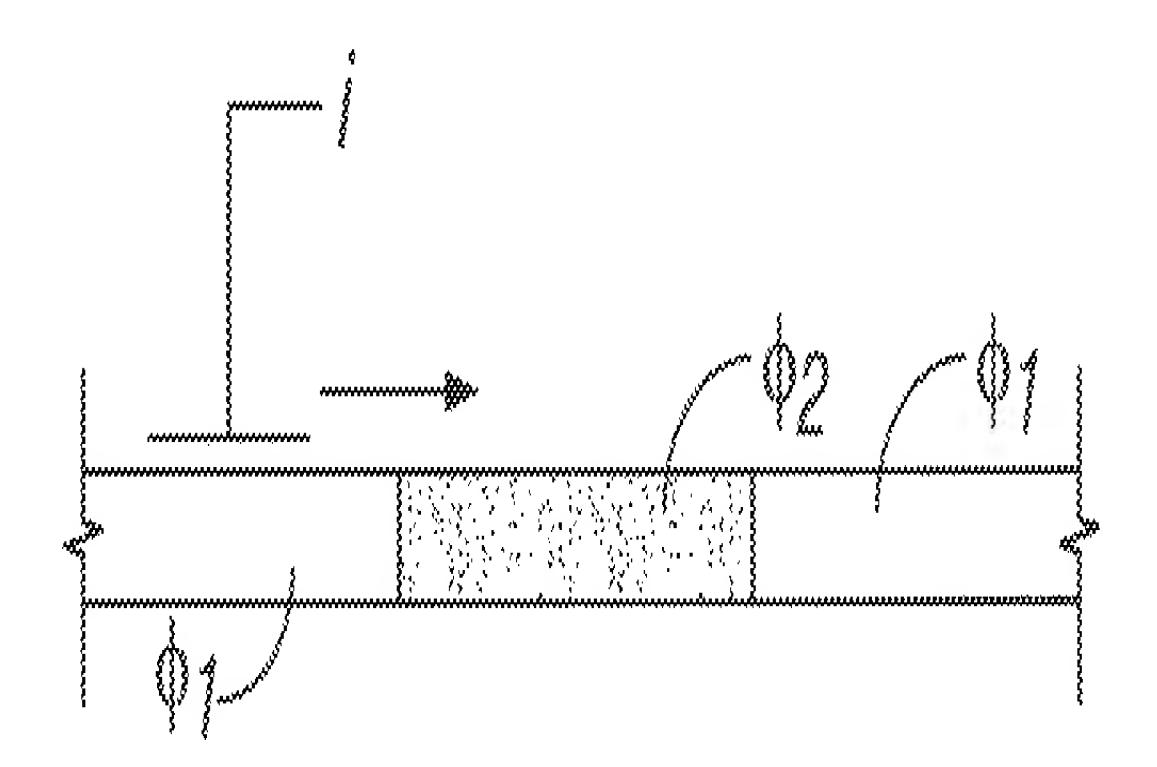
Er: Fermi Energy of Electrons

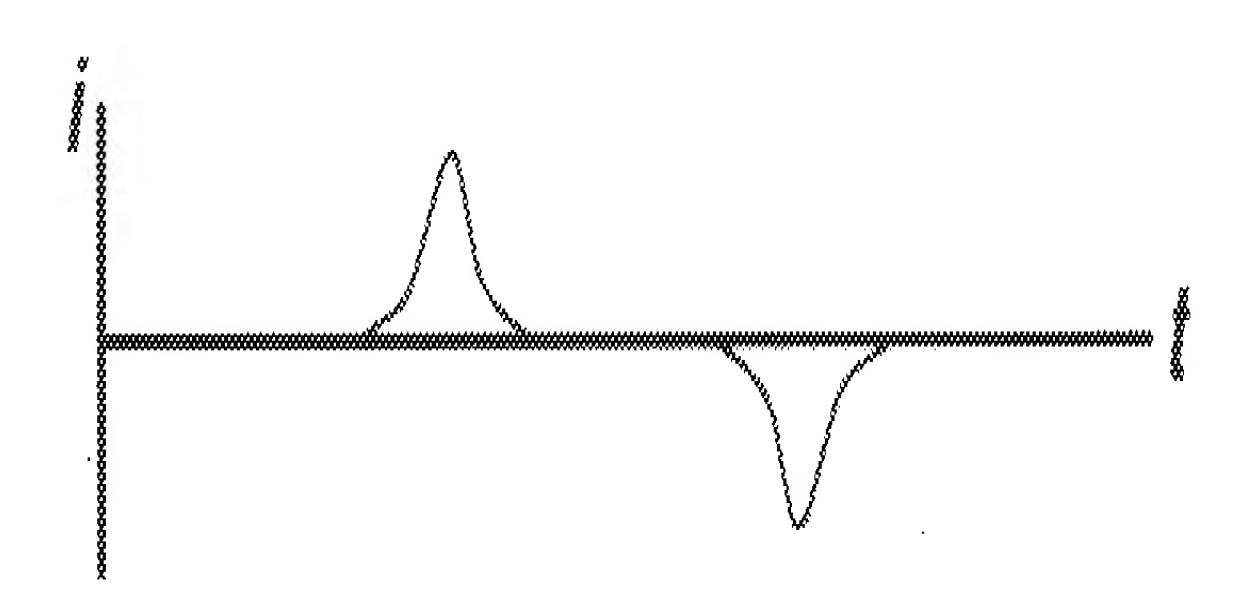
om: Work Function

FIG. 2

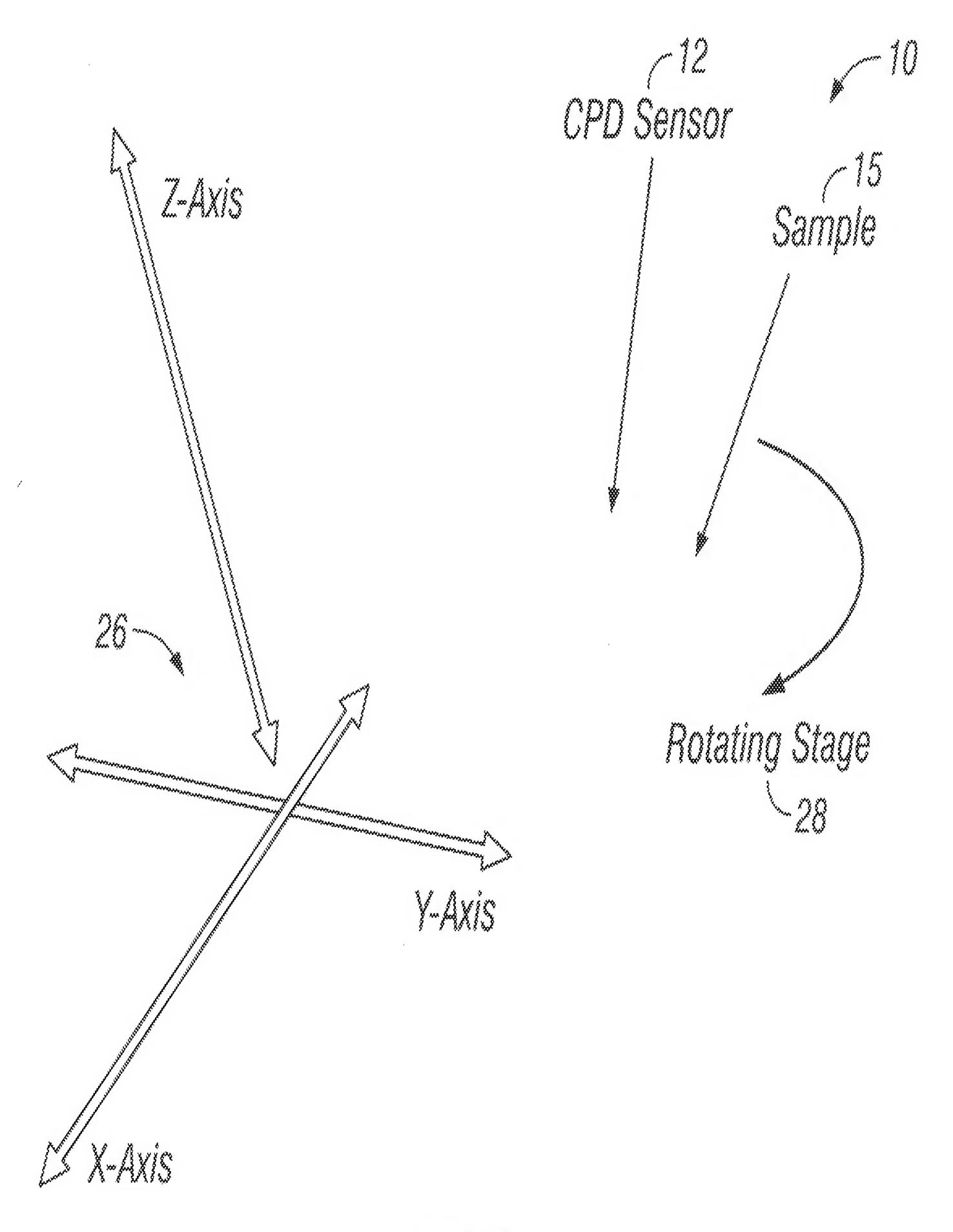


IU.3

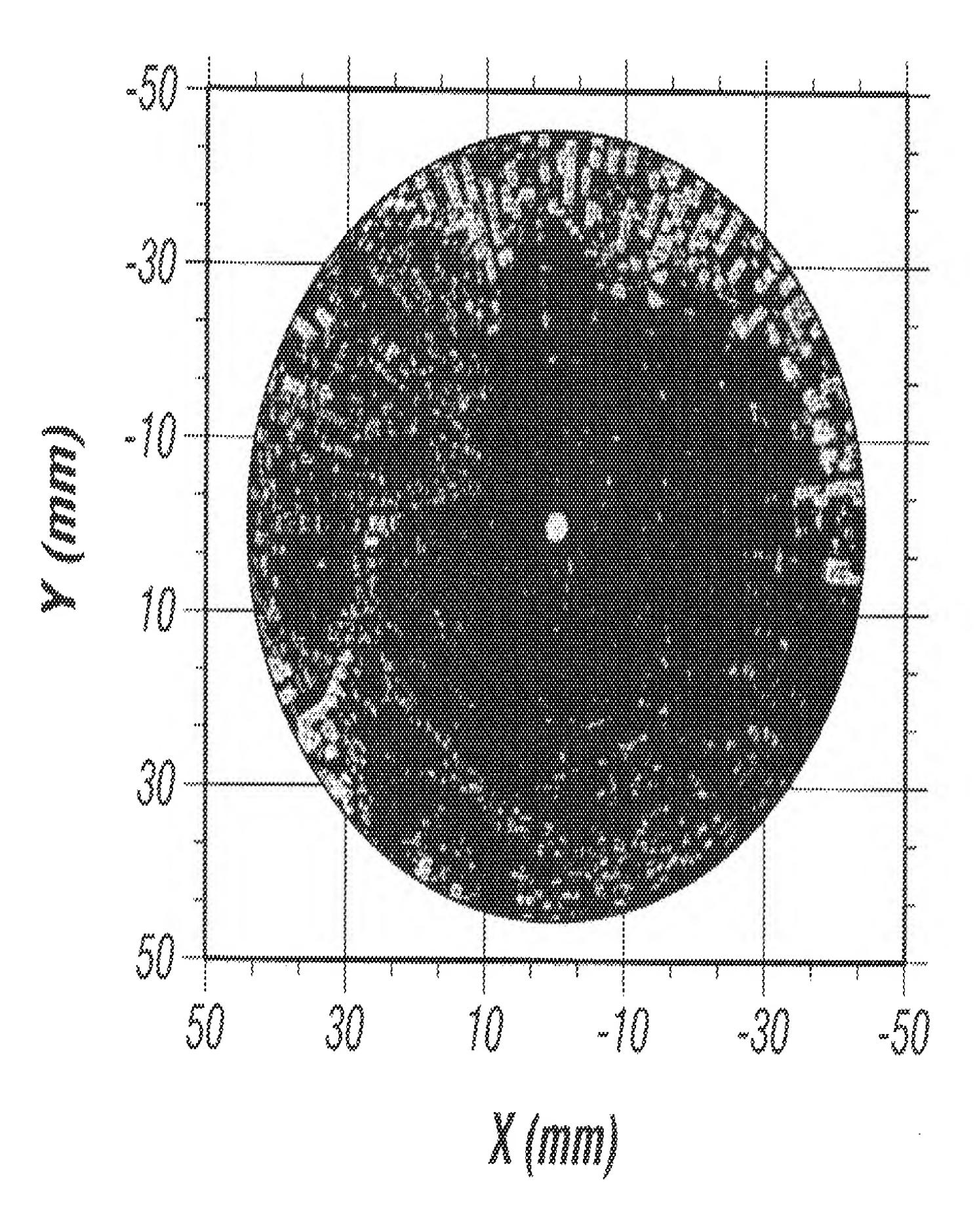




#10.4



IIC.5



IIC. O

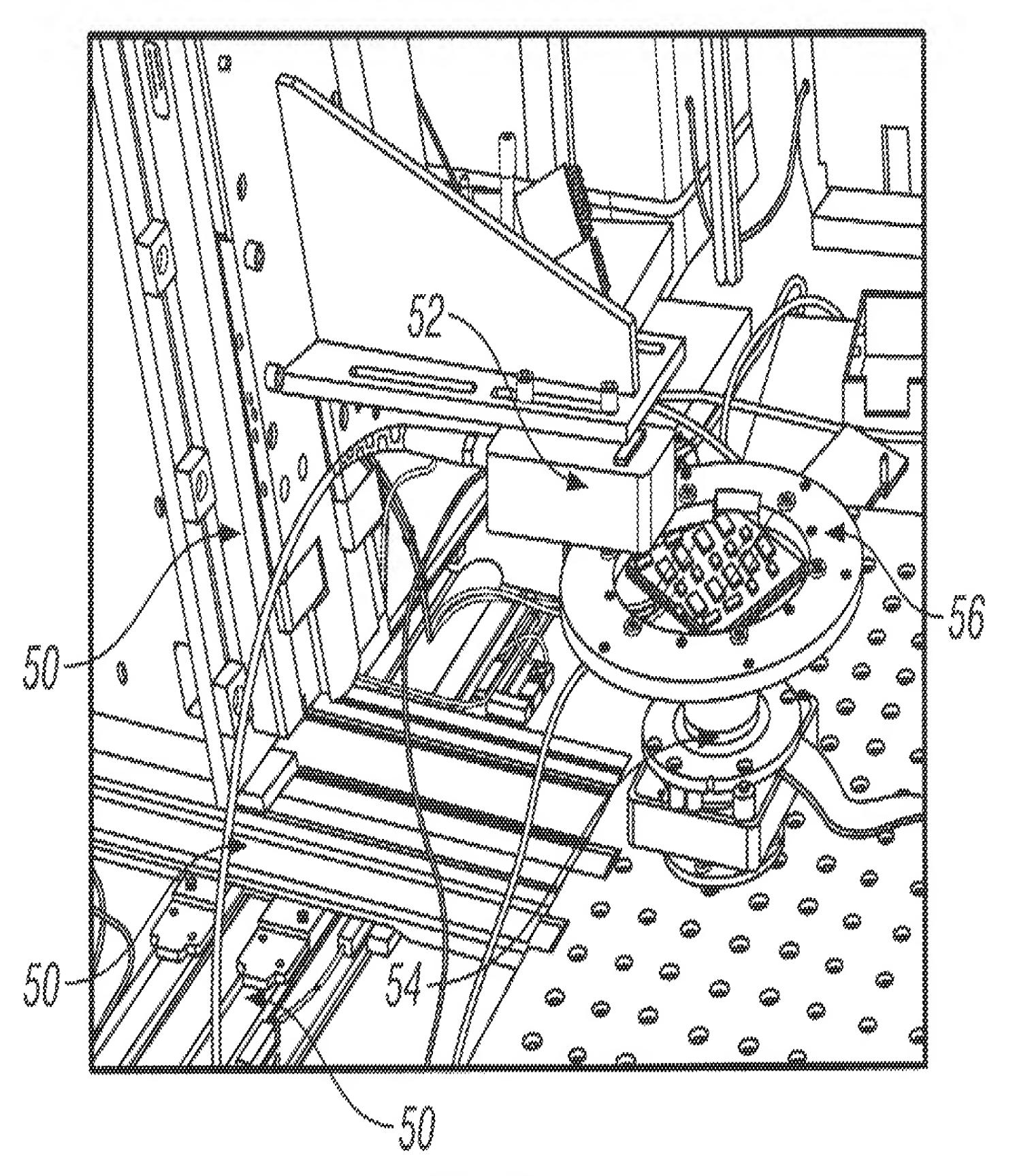
Select Contaminant and Surface Concentration

Choose Carrier Liquid and Create Solution

Prepare Wafer Surface via HF Dip and Clean

Dip Wafer Using Optimized Parameters

Characterize Contaminated Area (XPS, Auger, EDS)



ric. Om

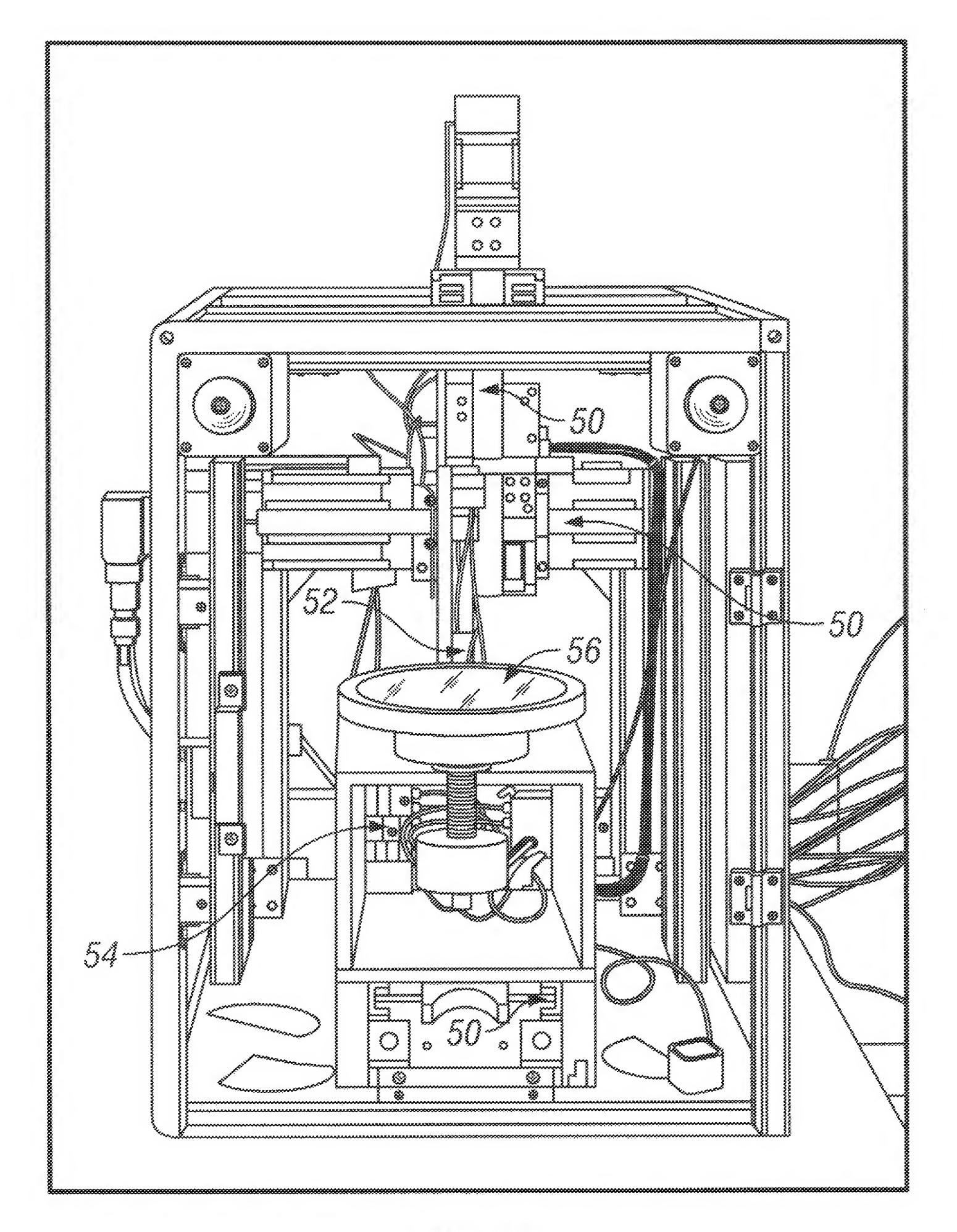
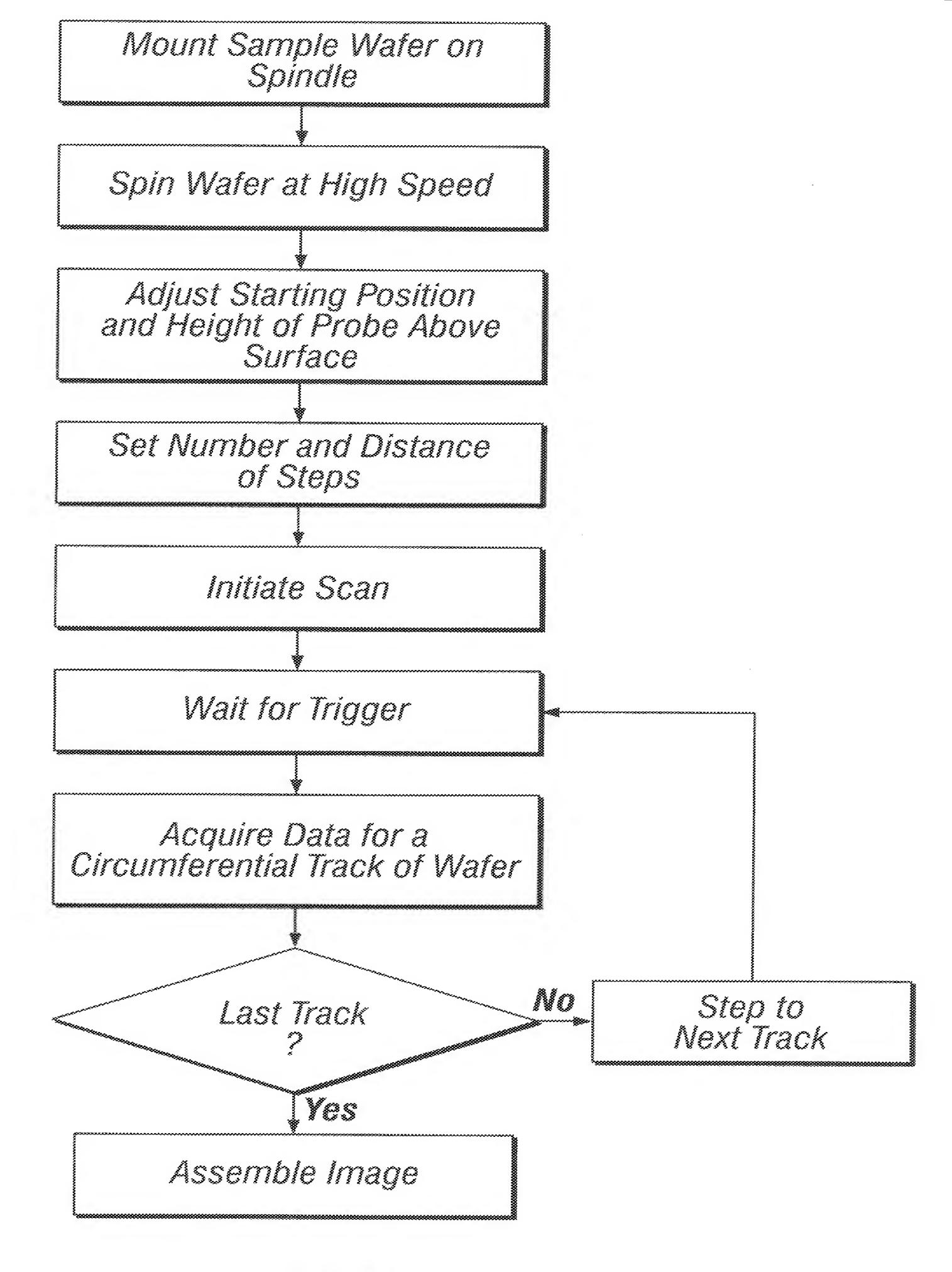


FIG.00



II.9

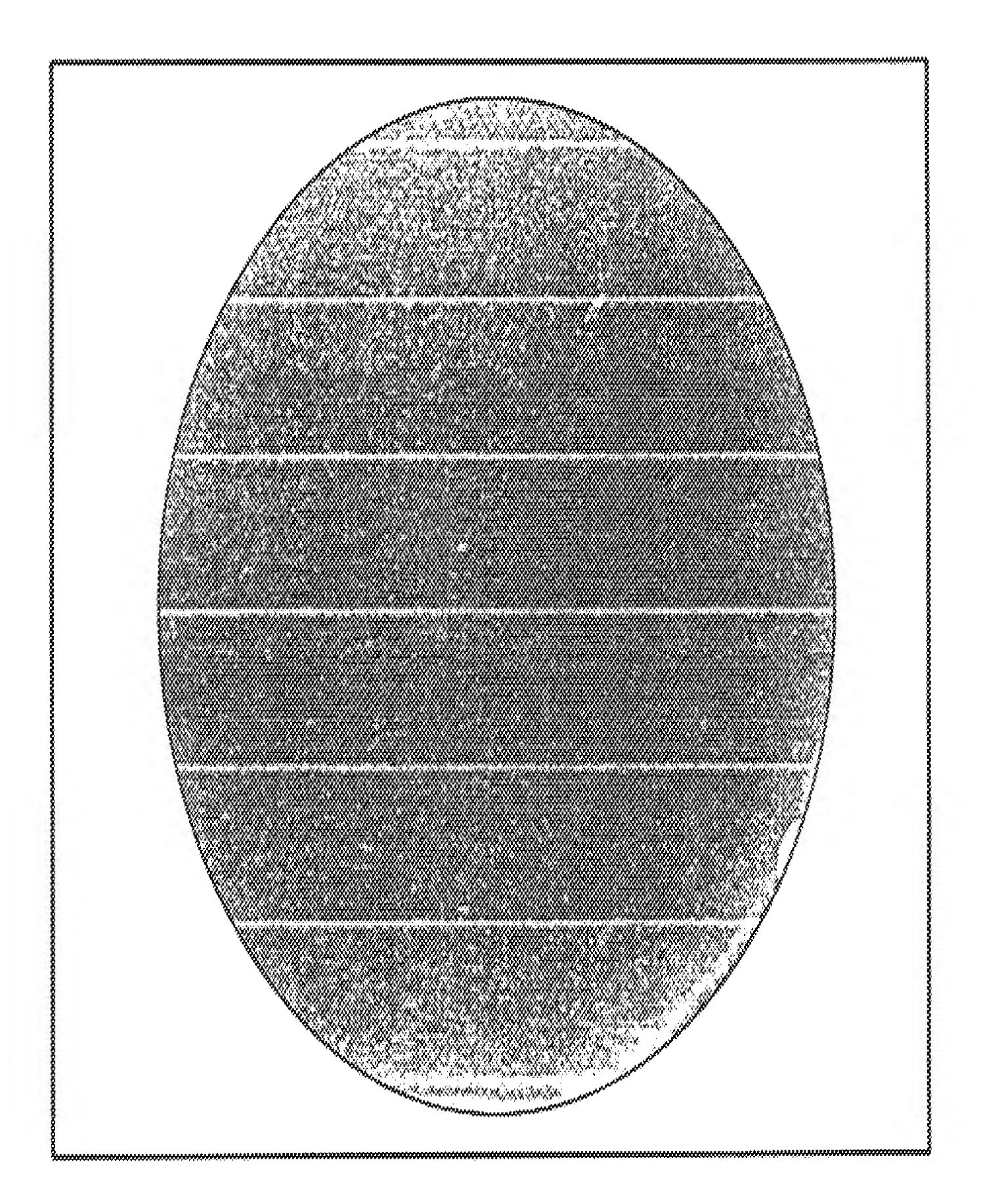


FIG. 10A

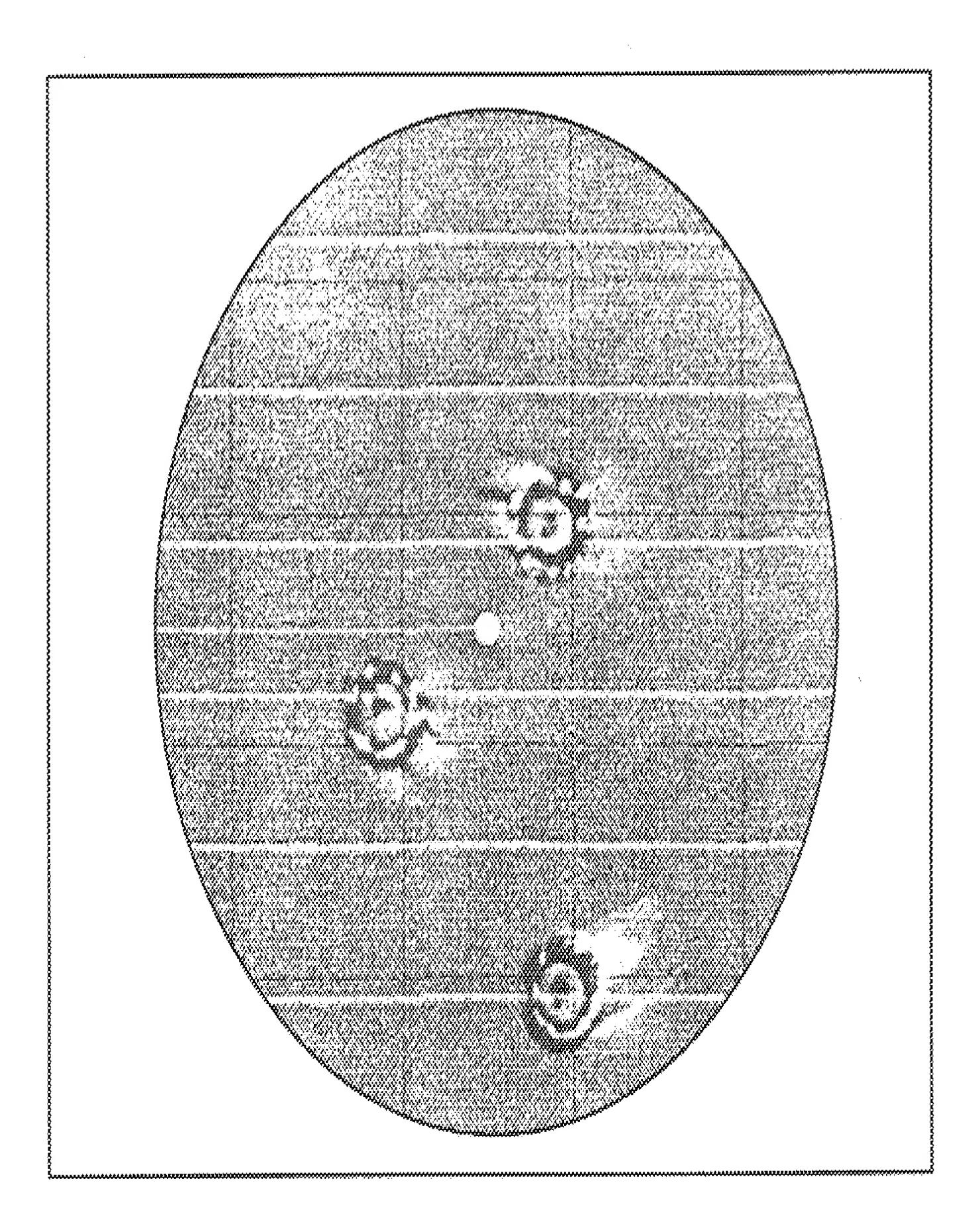


FIG. 100

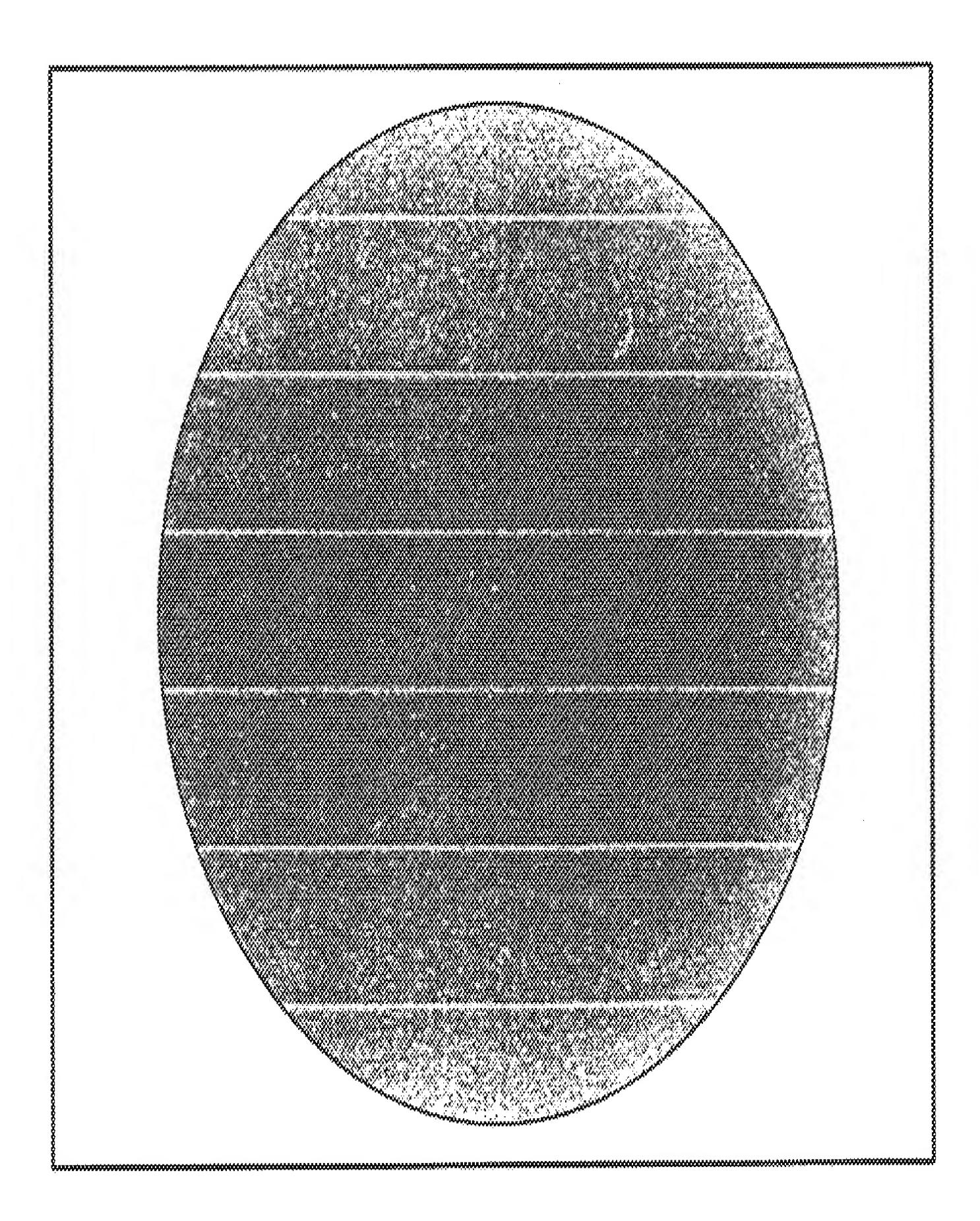


FIG. 11A

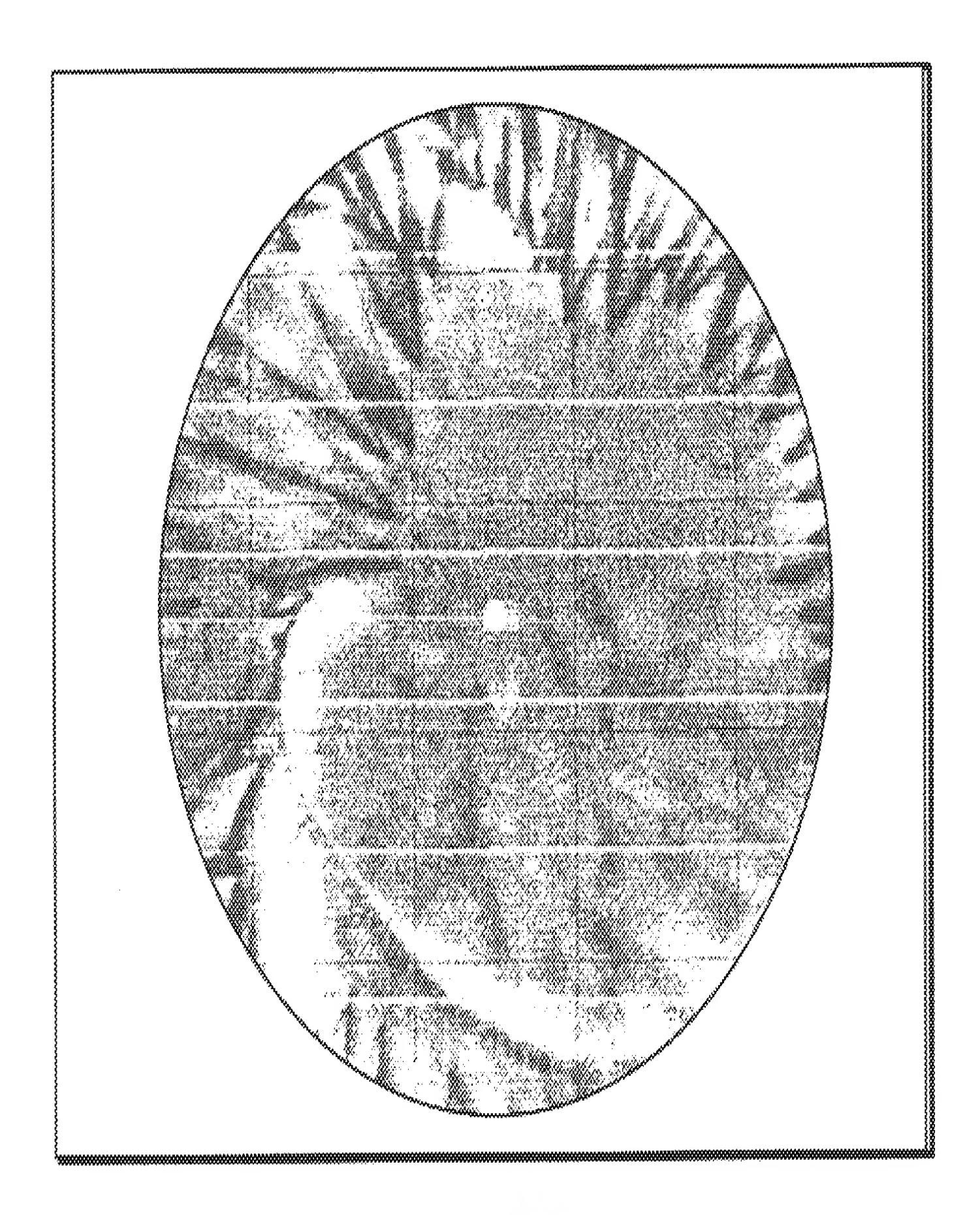


FIG. 11B

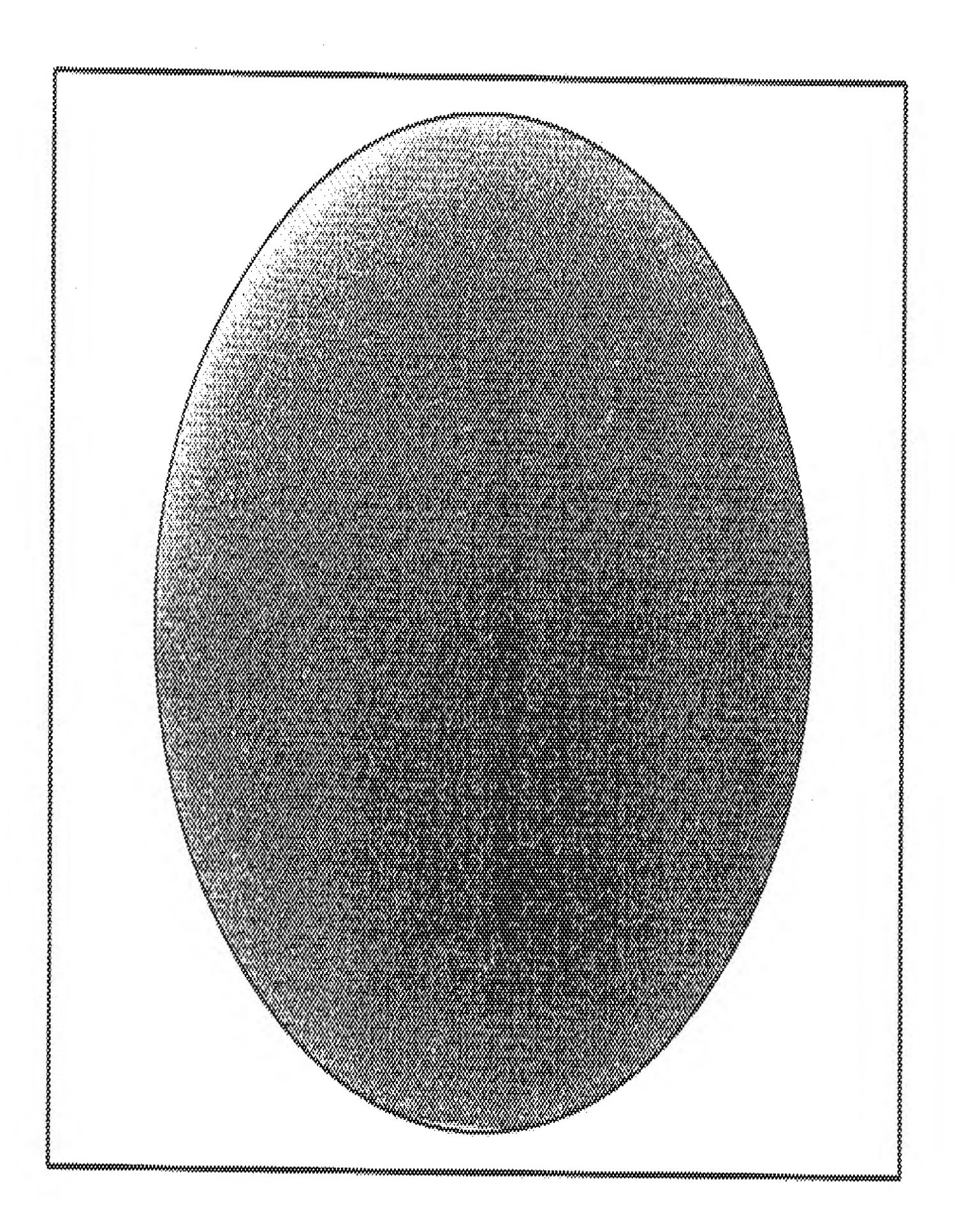
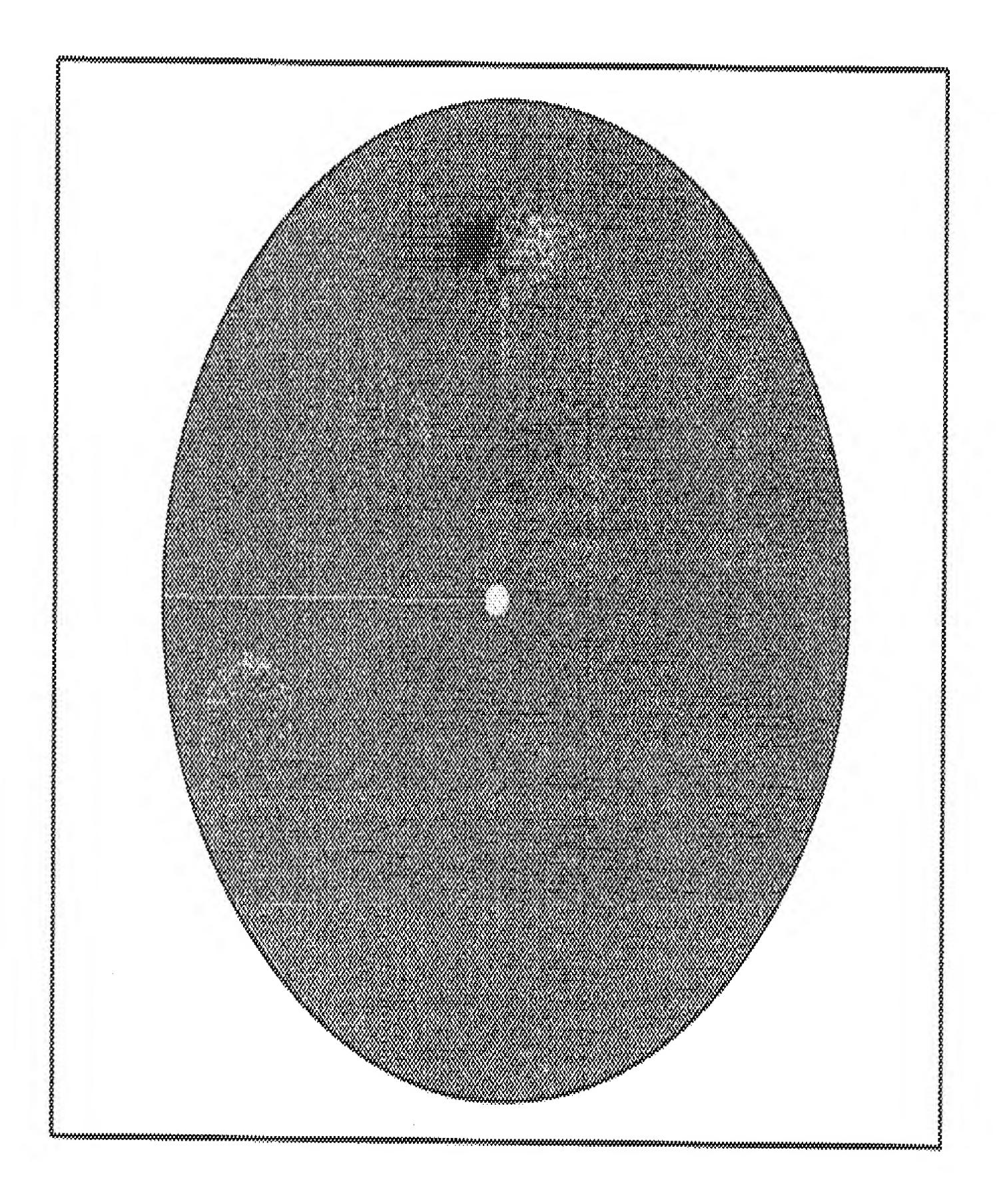
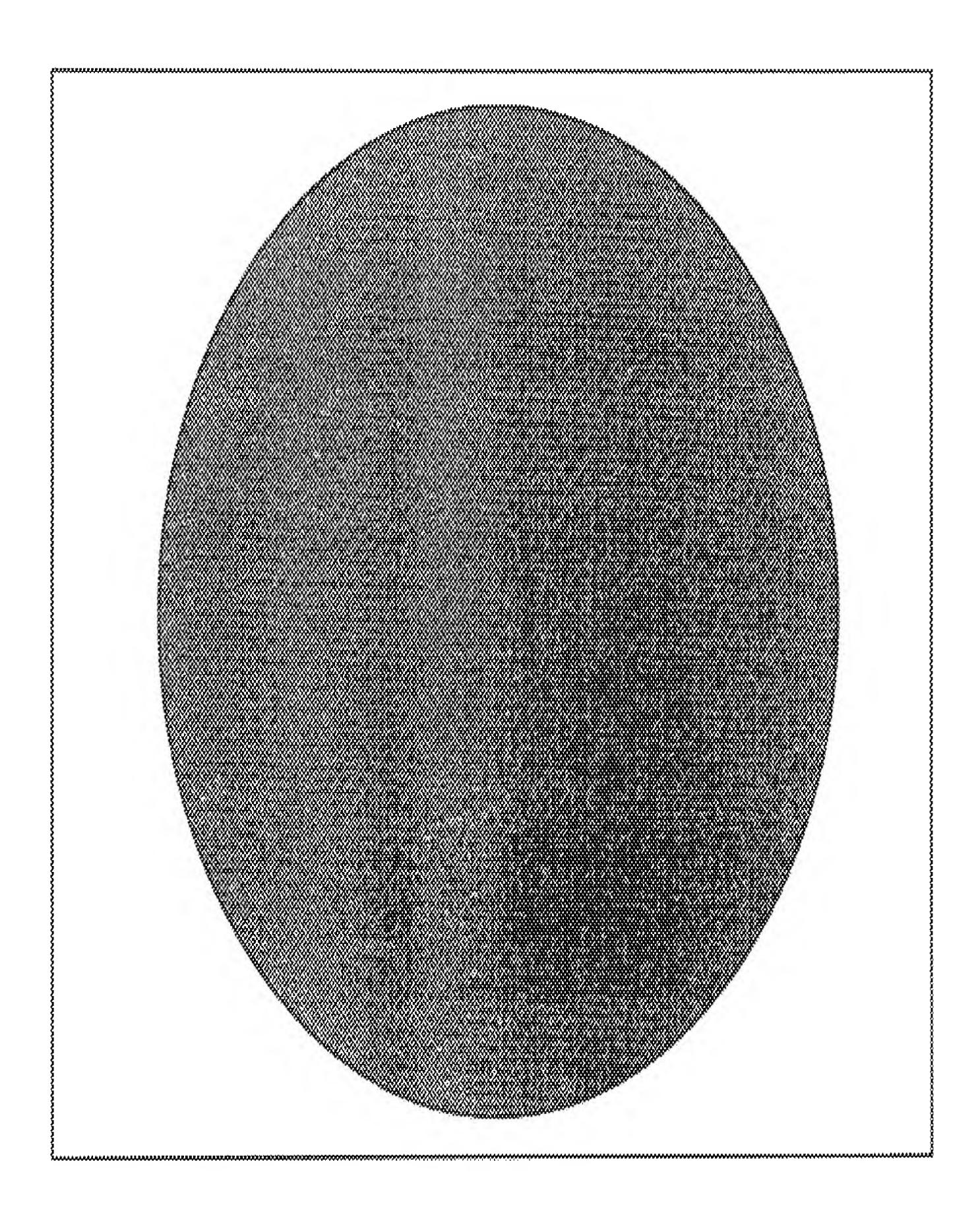


FIG. 12A



IIC. 120



"IQ. 13A

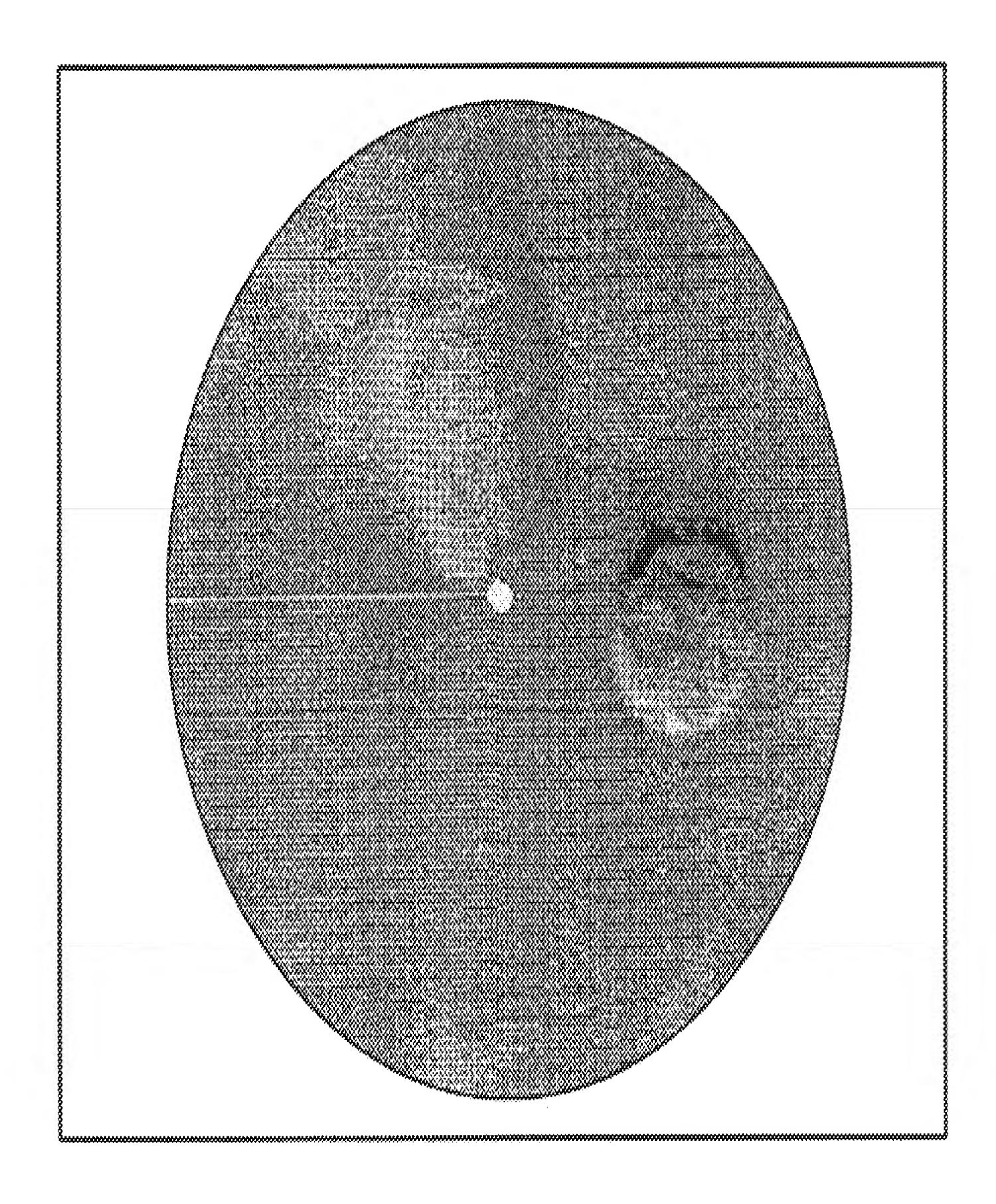


FIG. 13D

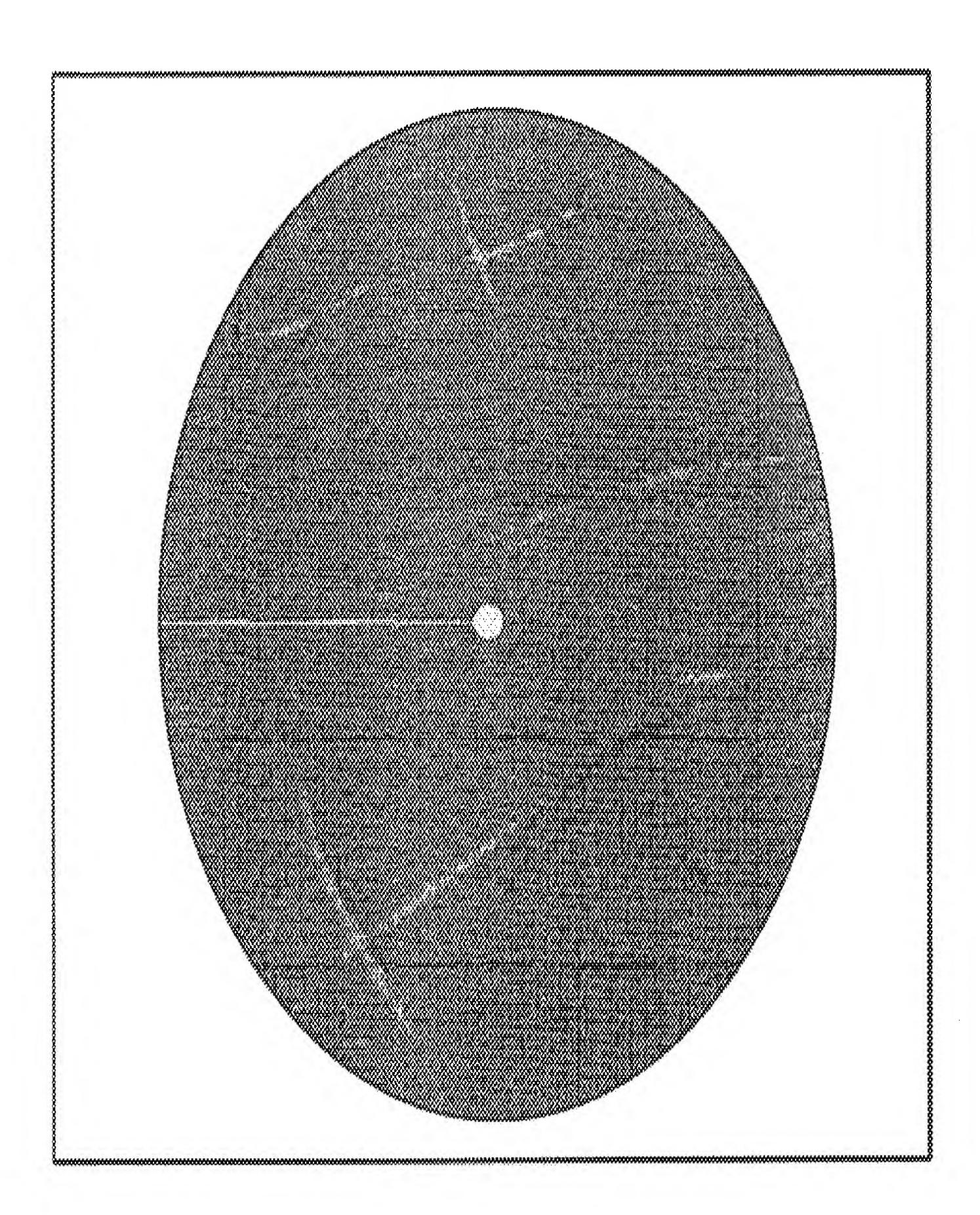
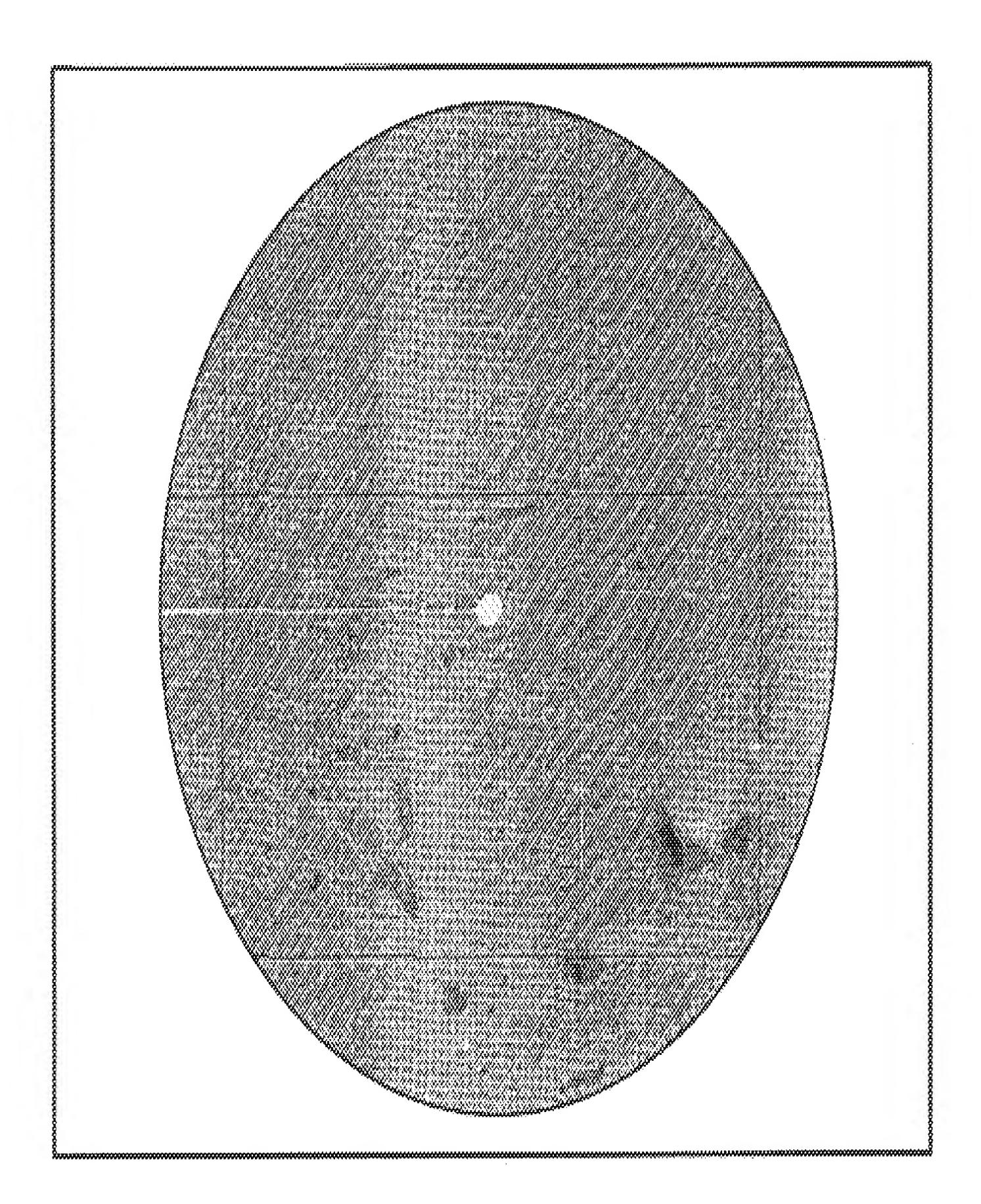


FIG. 14



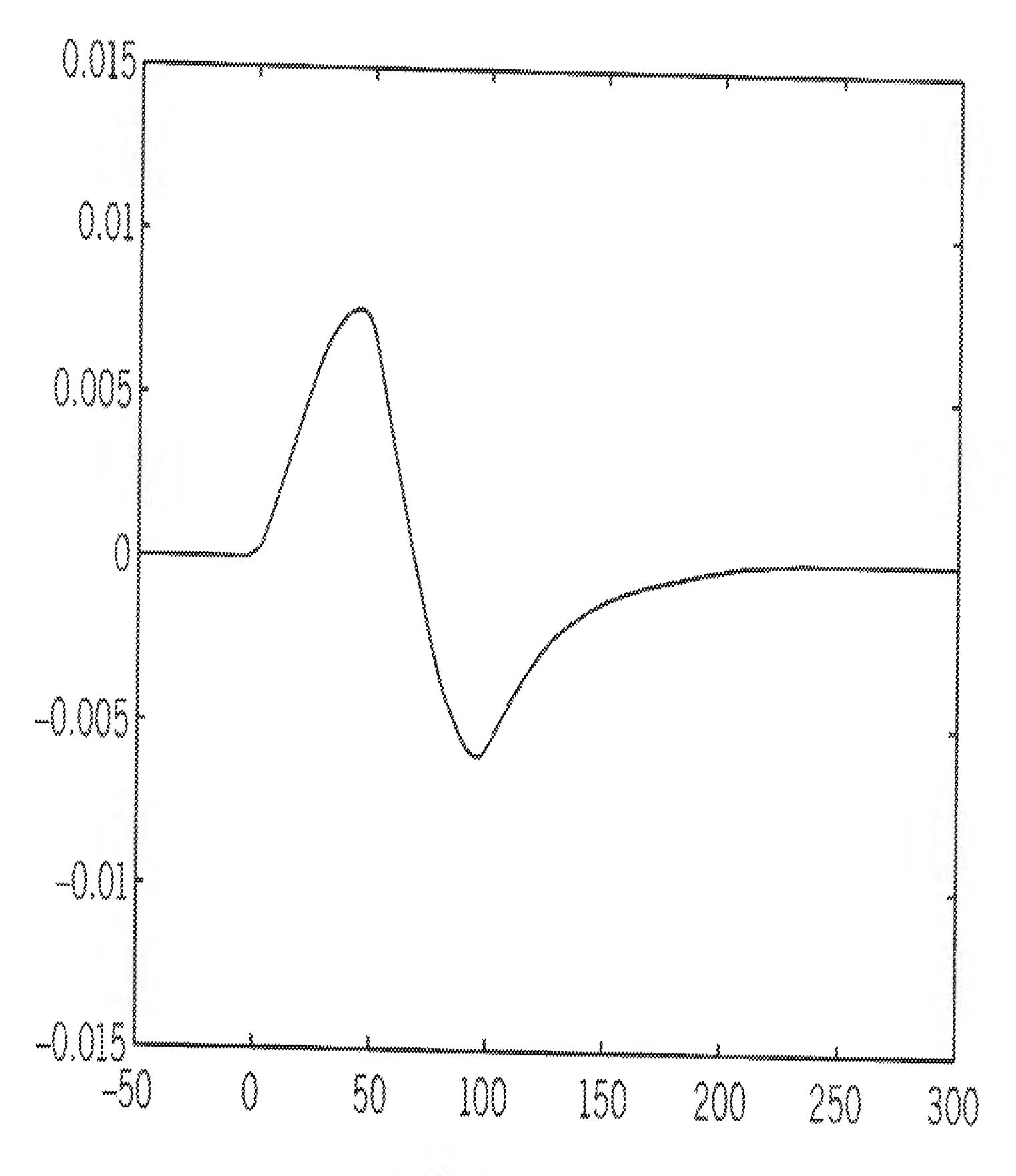
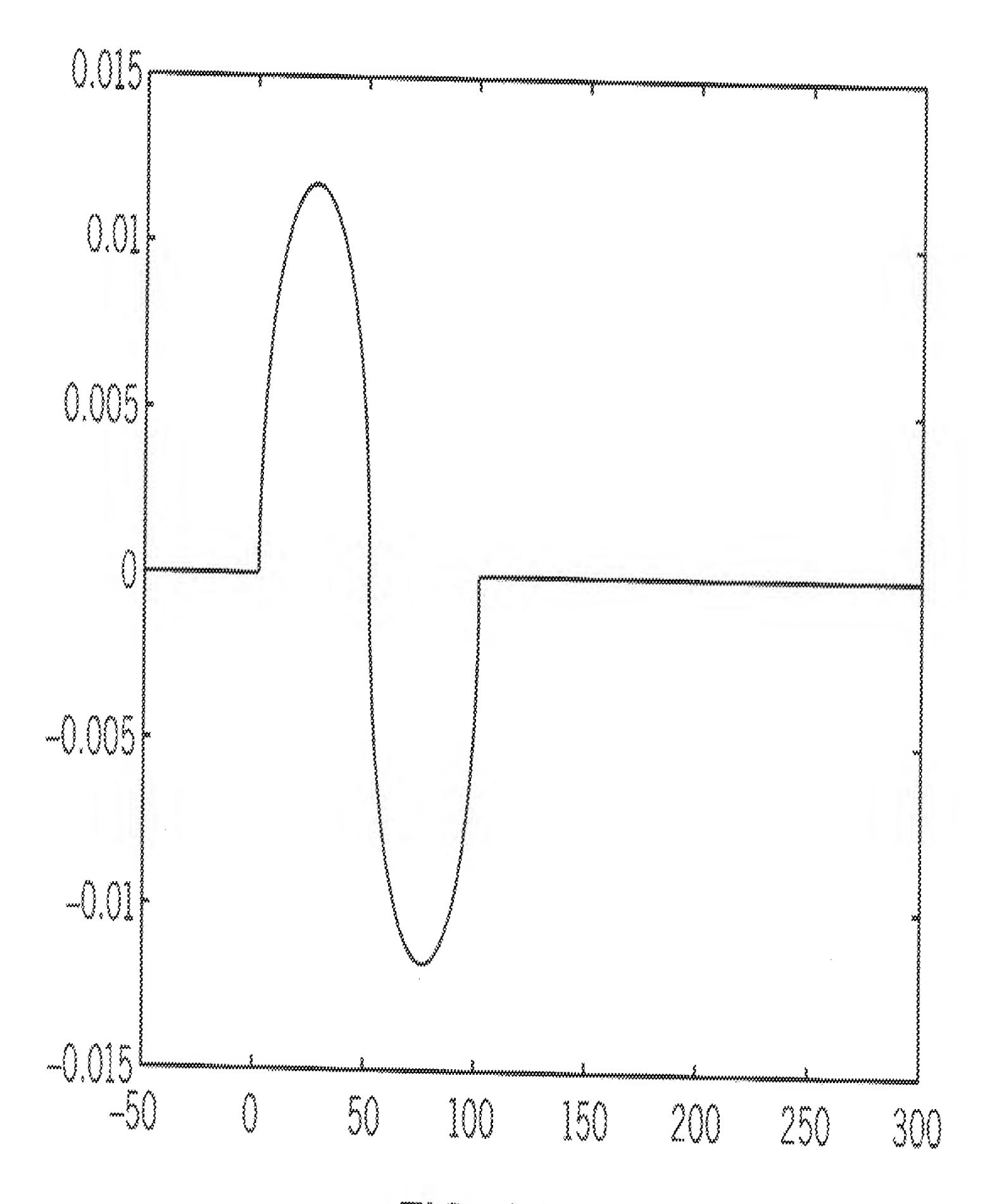


FIG. 16



POSITIONING THE NVCPD SENSOR ABOVE THE WAFER

DETECTING AT LEAST THREE FEATURES ON THE SURFACE OF THE WAFER

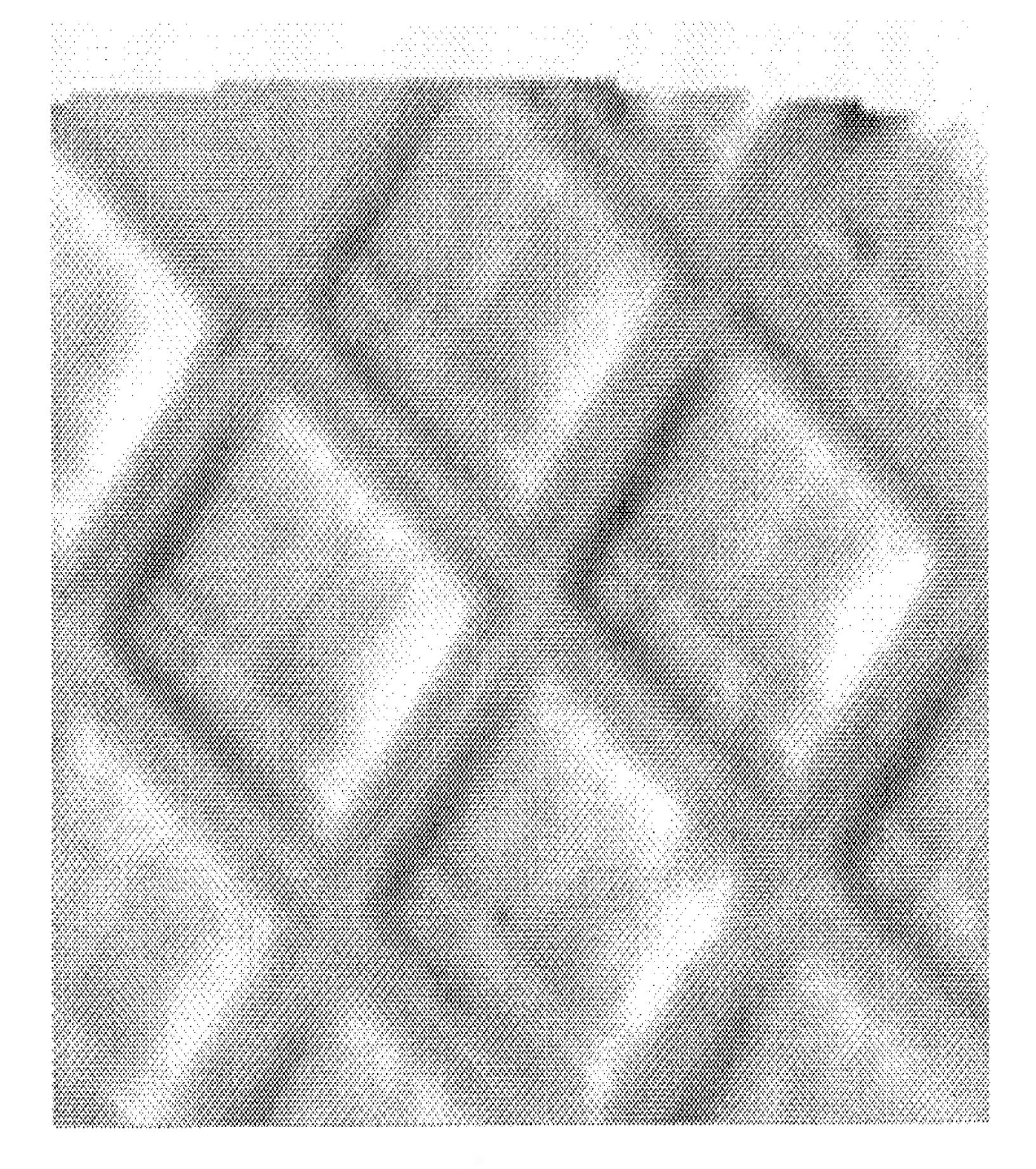
CALCULATING THE CENTER OF THE WAFER.

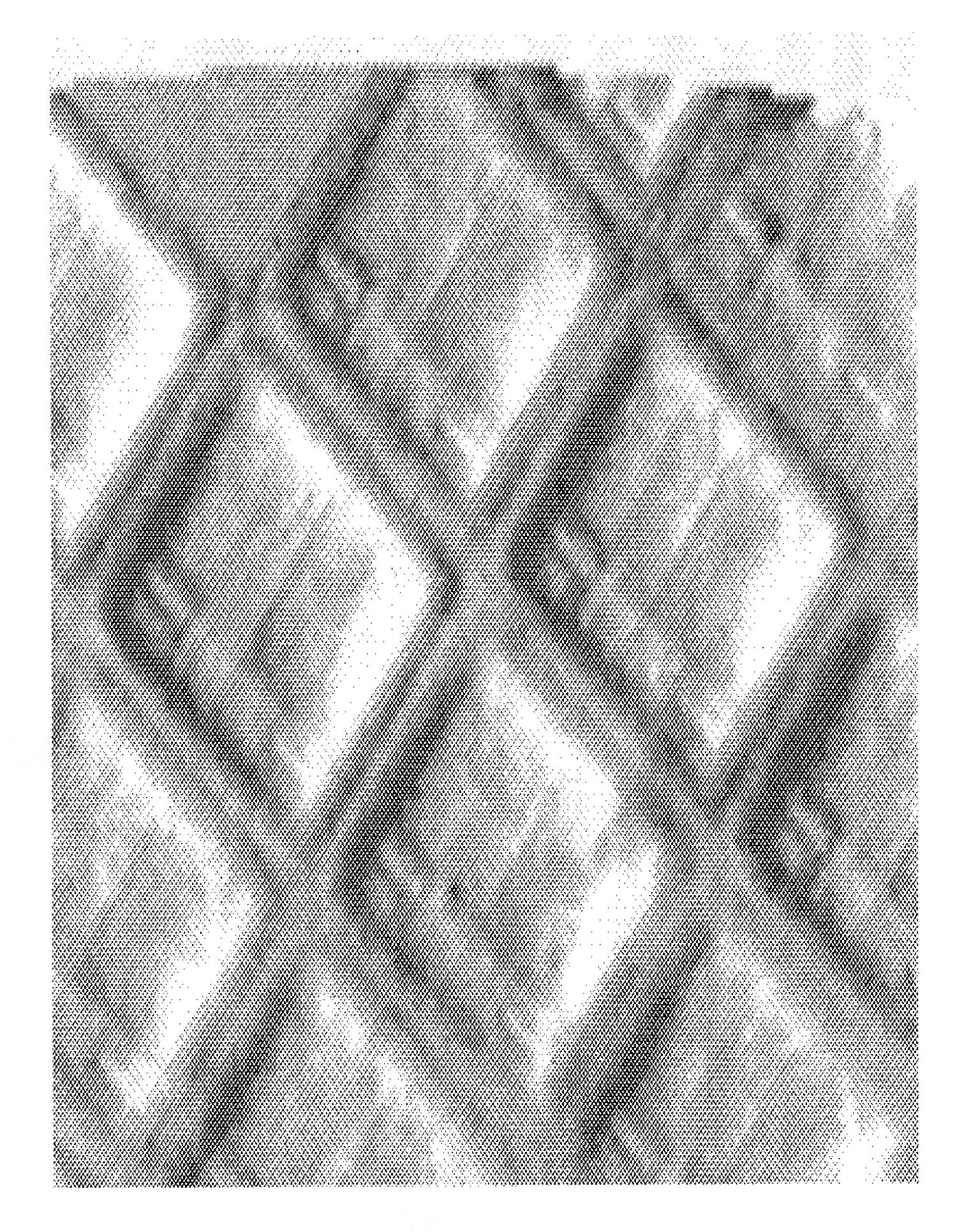
POSITIONING THE HEIGHT SENSOR ABOVE THE CENTER OF THE WAFER

MOVING THE HEIGHT SENSOR TO THE OUTER EDGE OF THE WAFER.

DETERMINING A HEIGHT PROFILE OF THE WAFER.

POSITIONING THE nVCPD
SENSOR AT AN APPROPRIATE
SCAN HEIGHT BASED ON THE
WAFER HEIGHT PROFILE.





m (C). 20

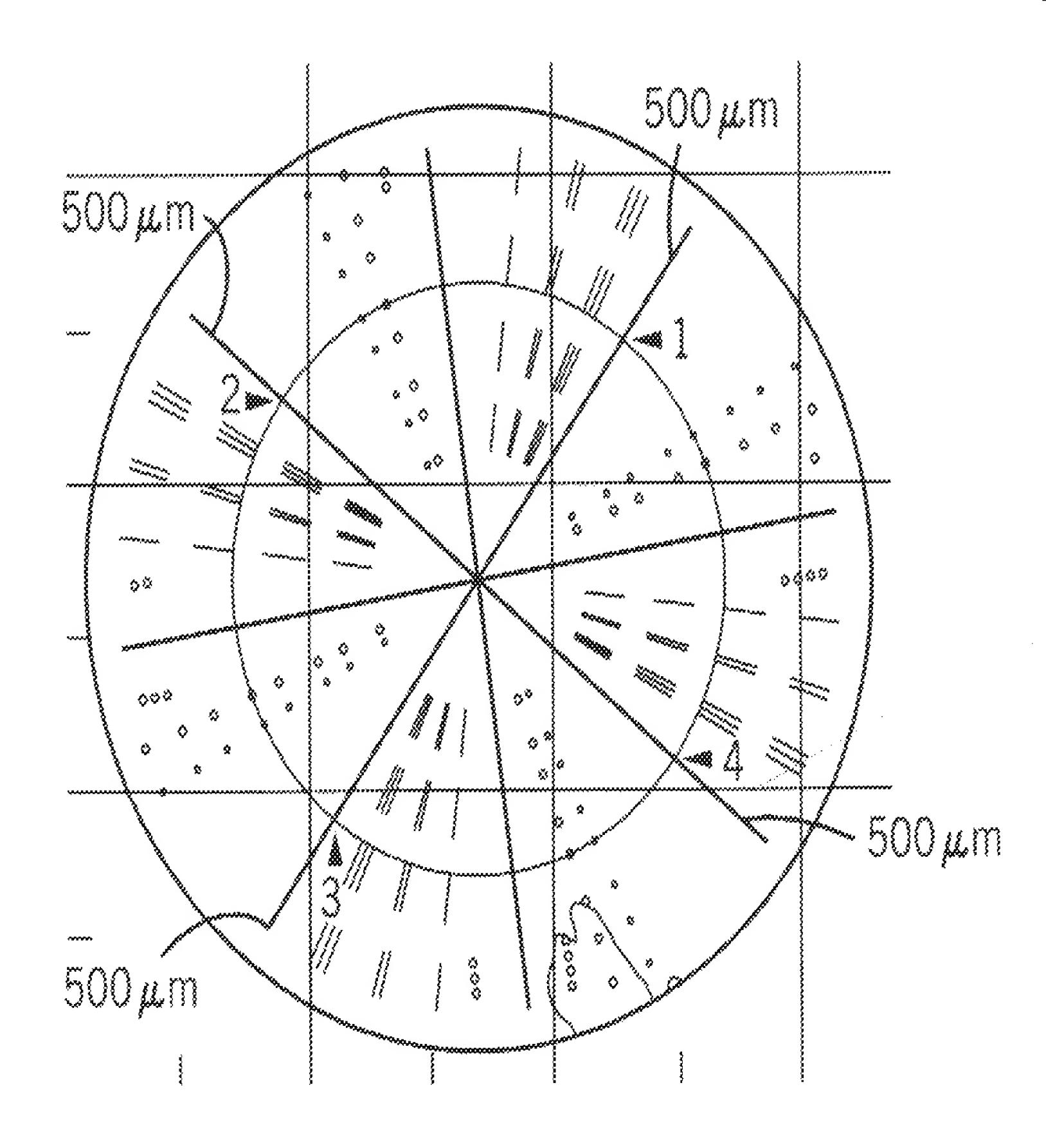
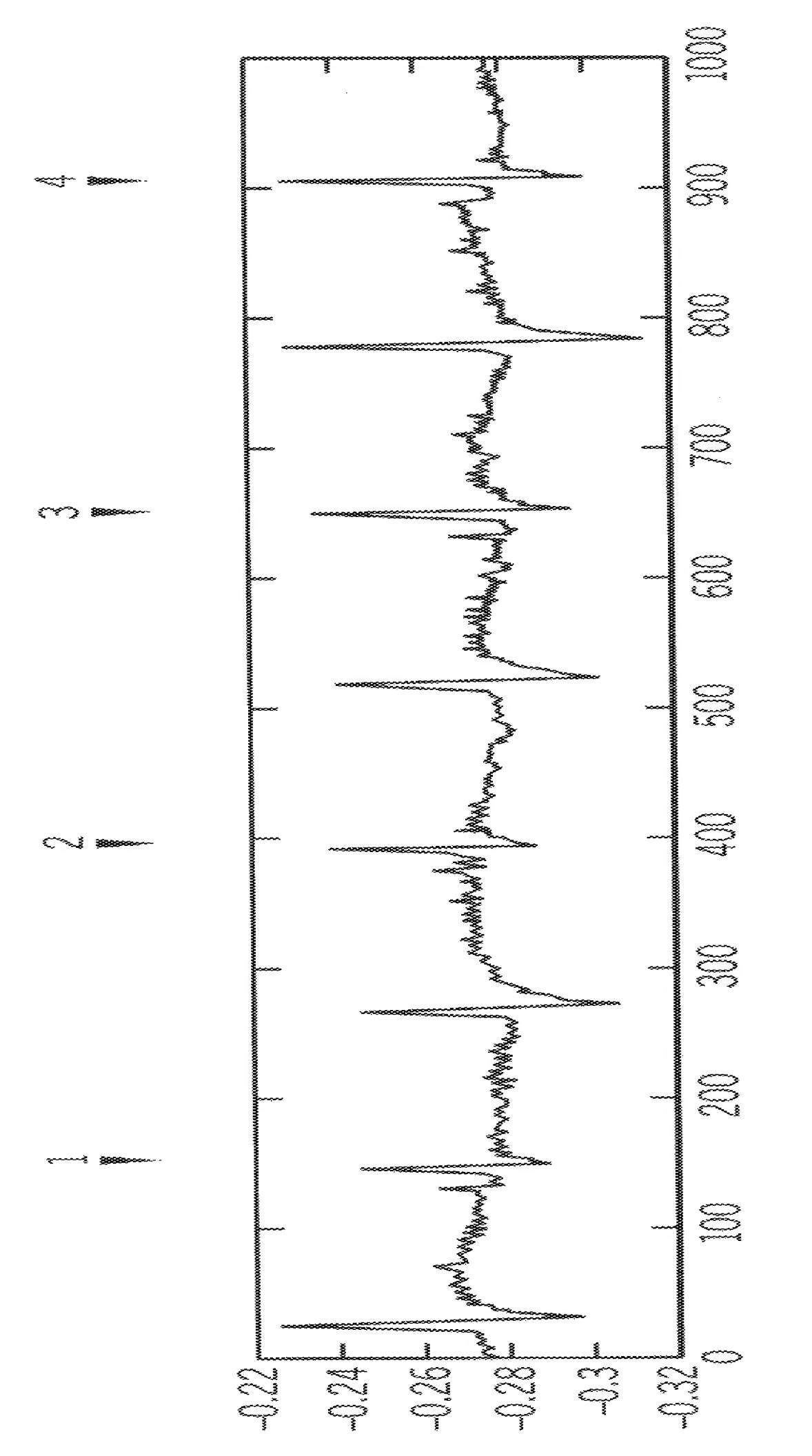
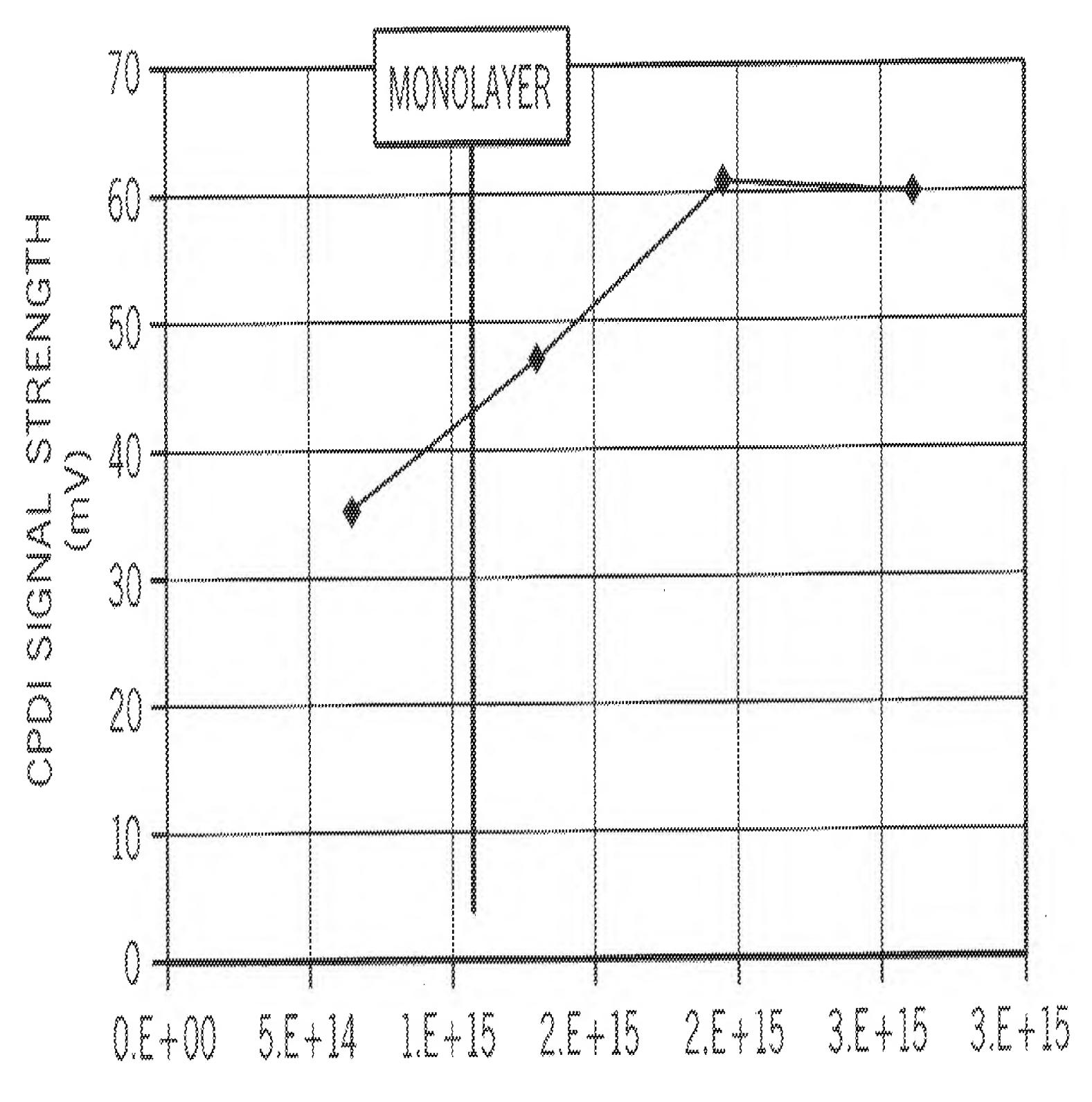


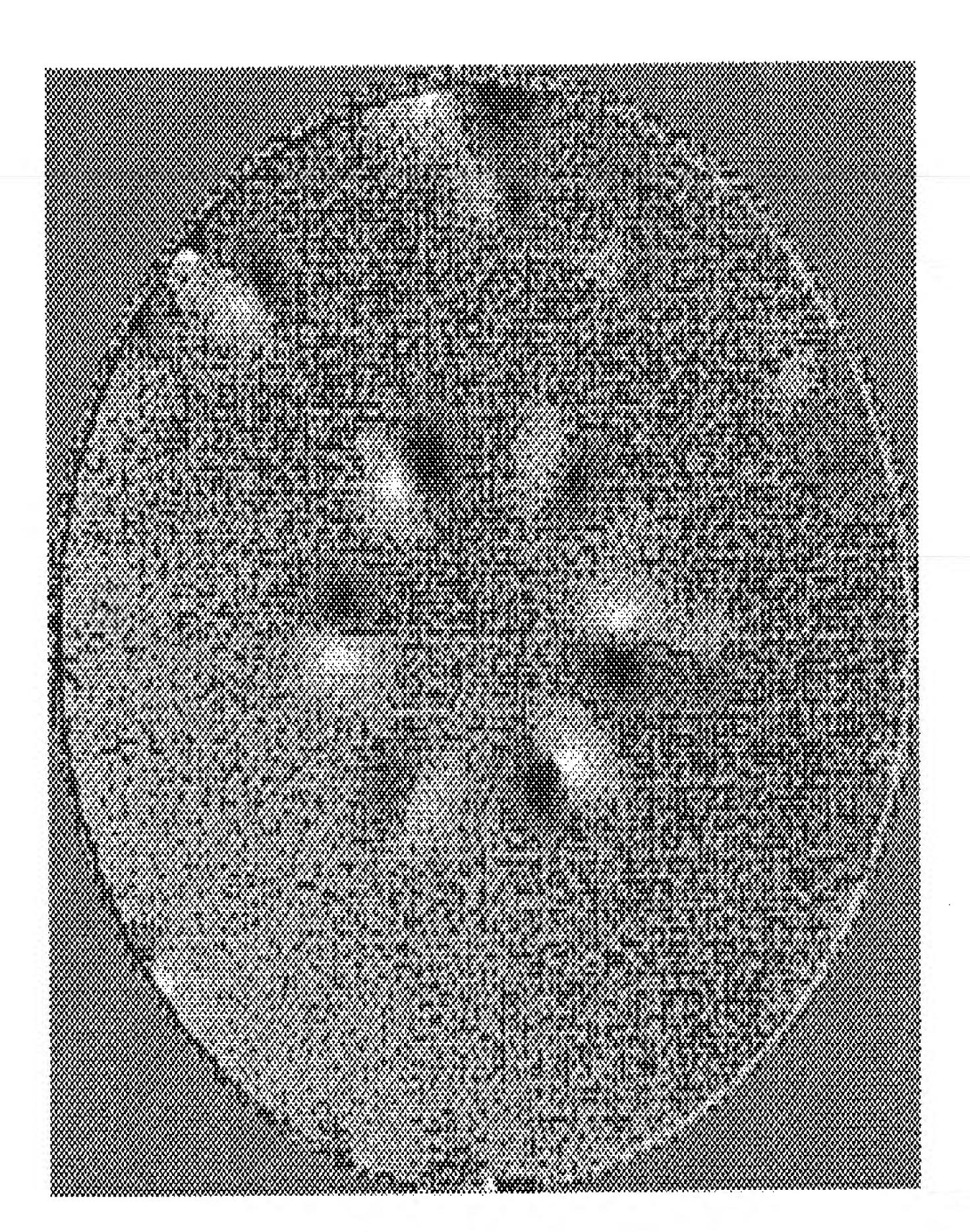
FIG. 21A



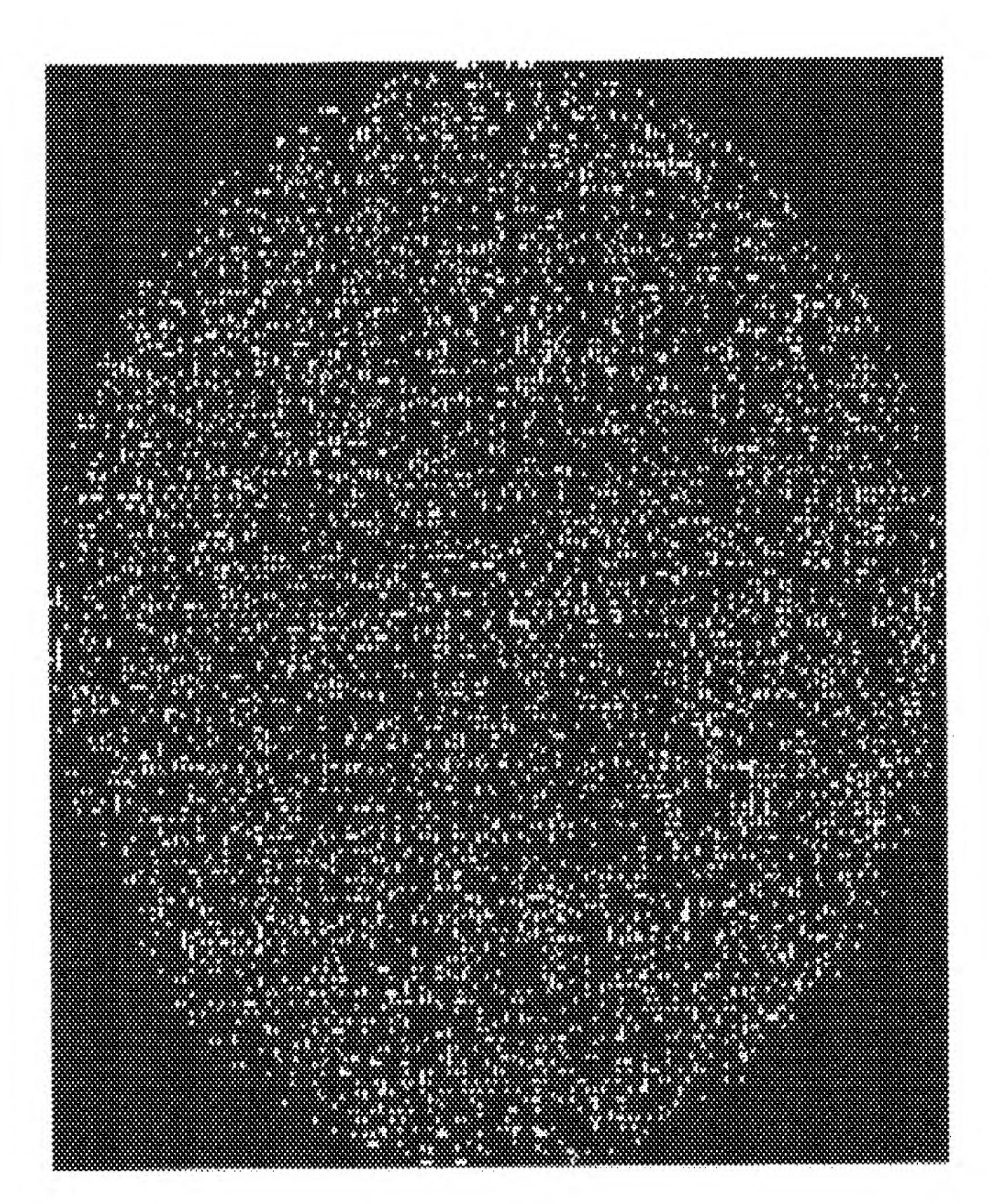


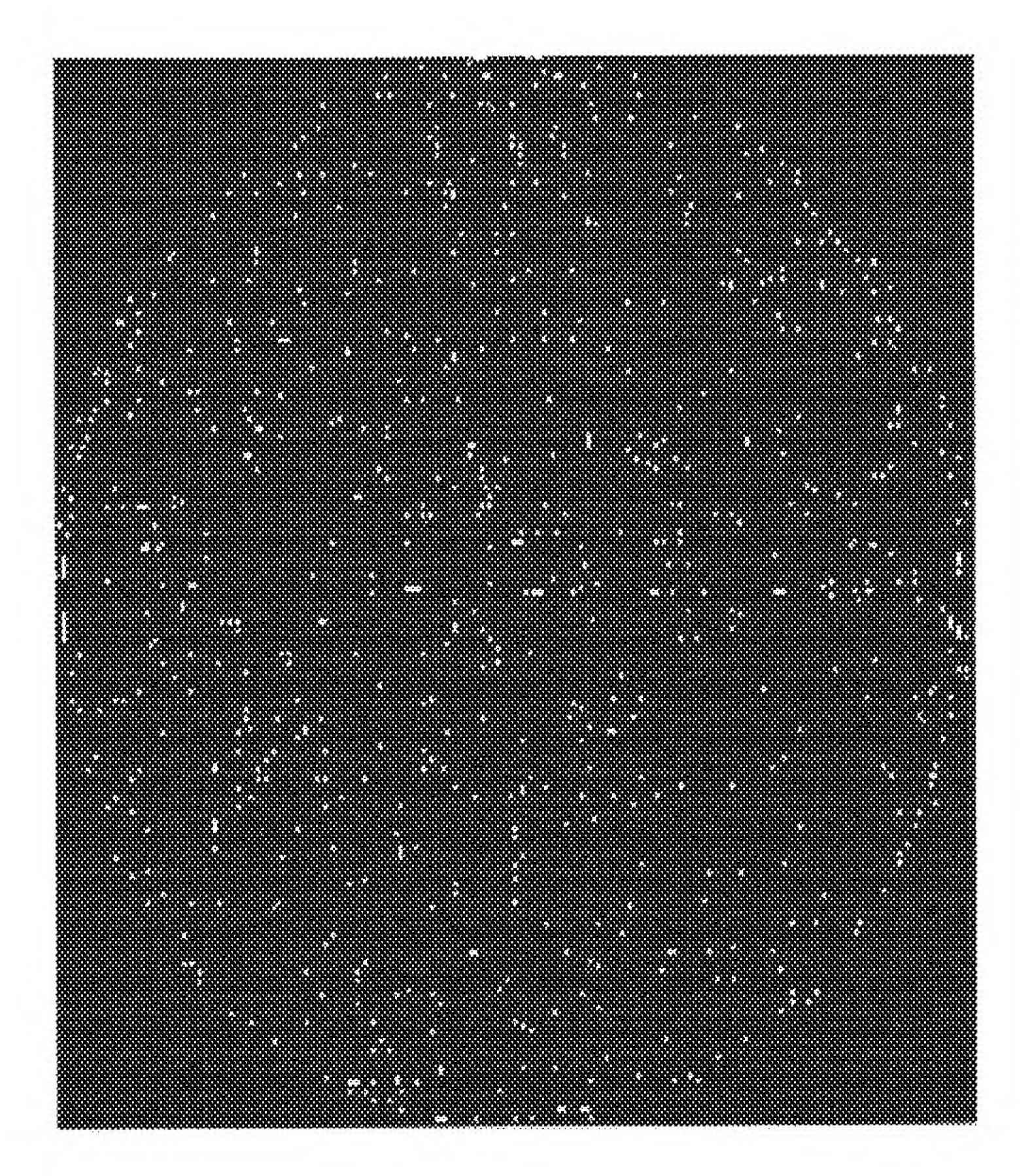
SURFACE DENSITY OF GOLD

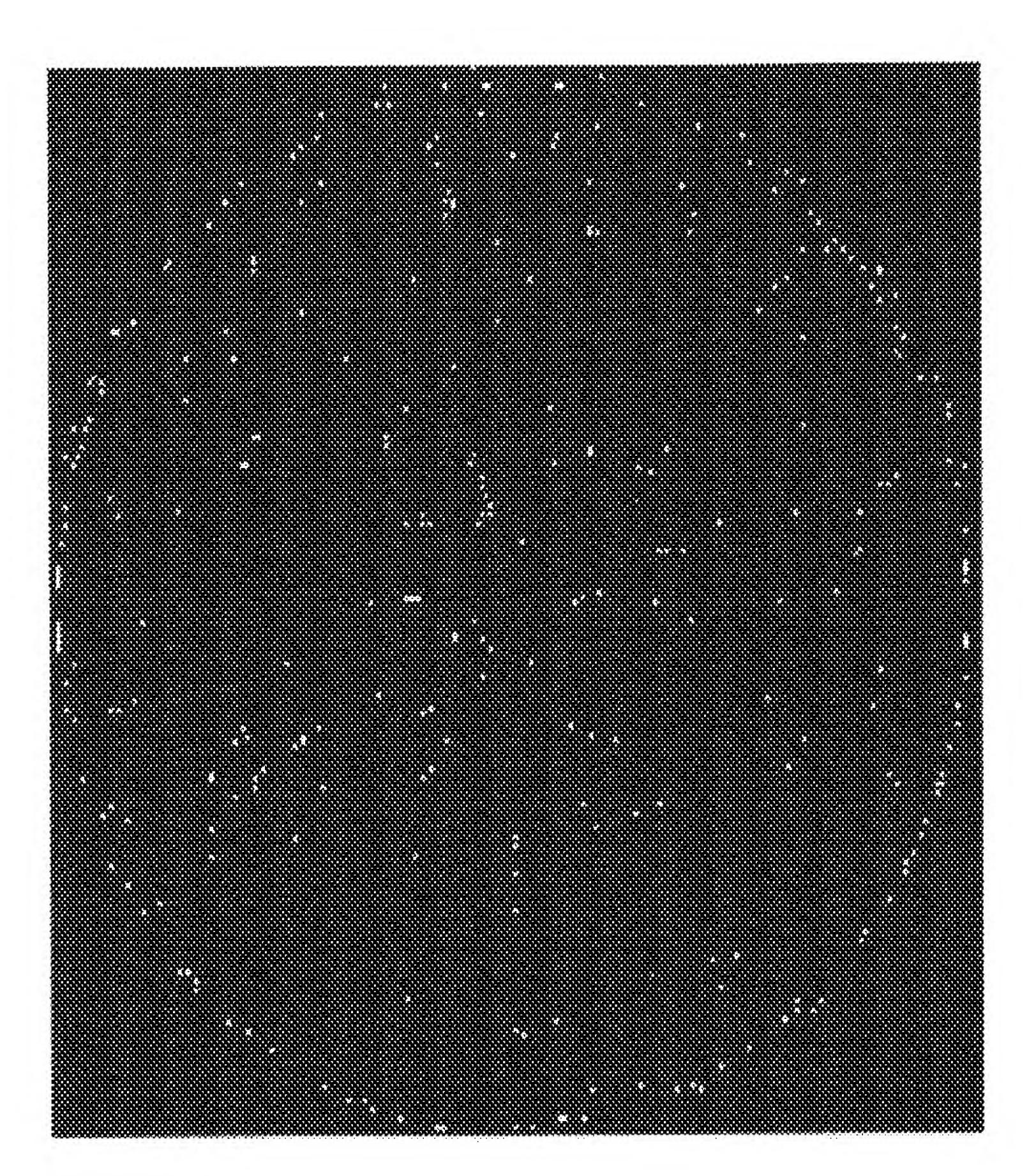
(ATOMS / cm2)

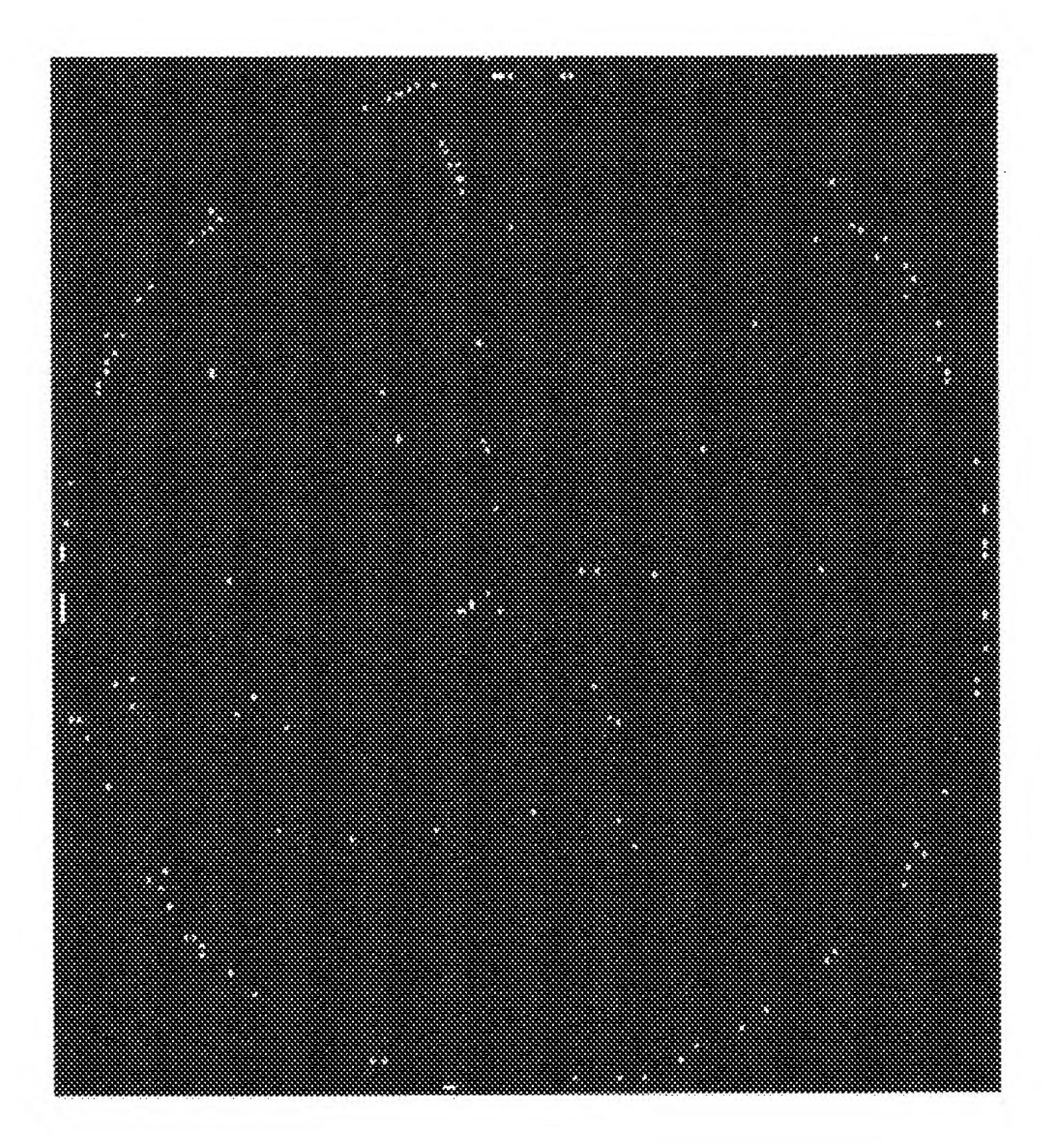


"10.22A









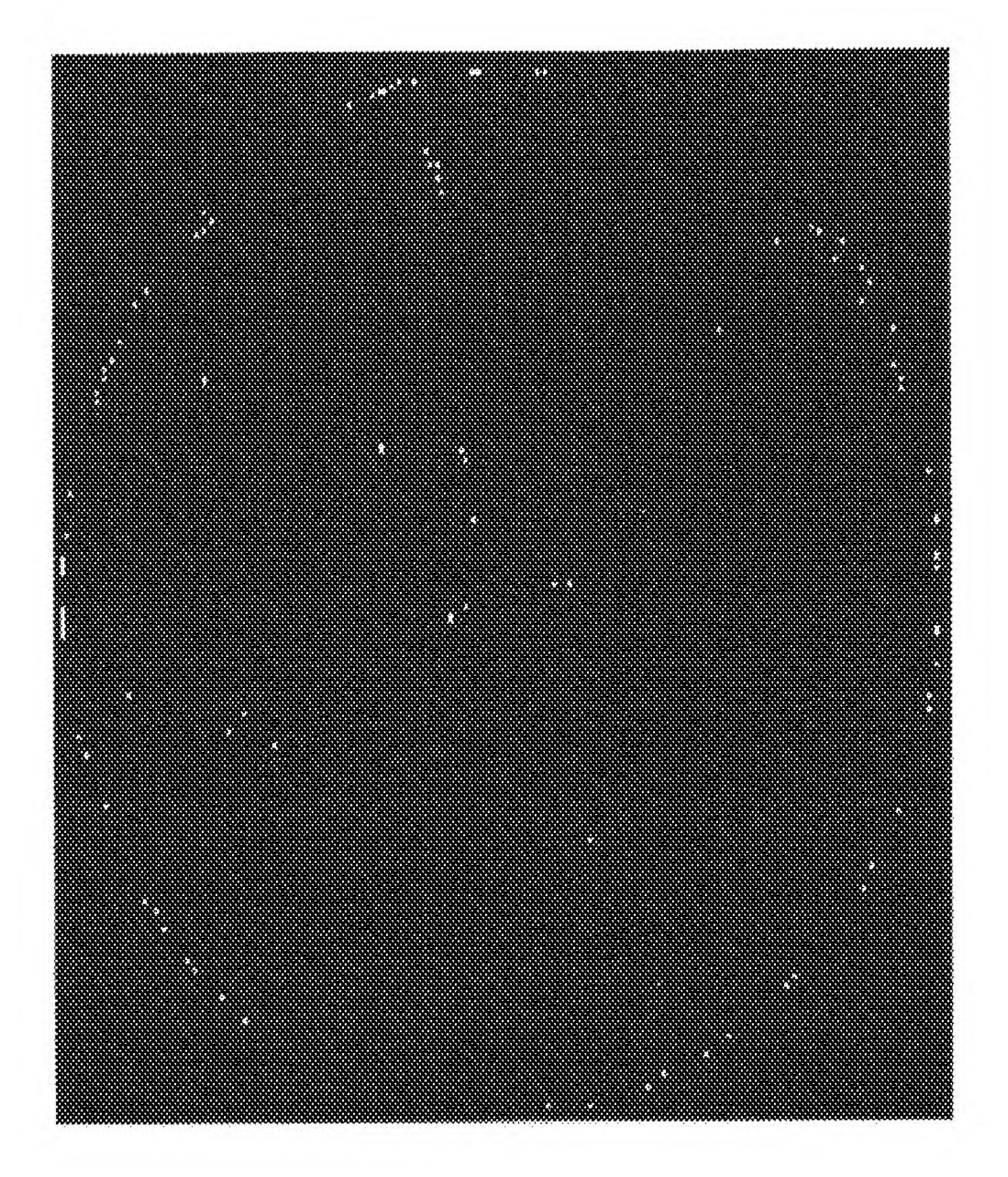


FIG. 22 F

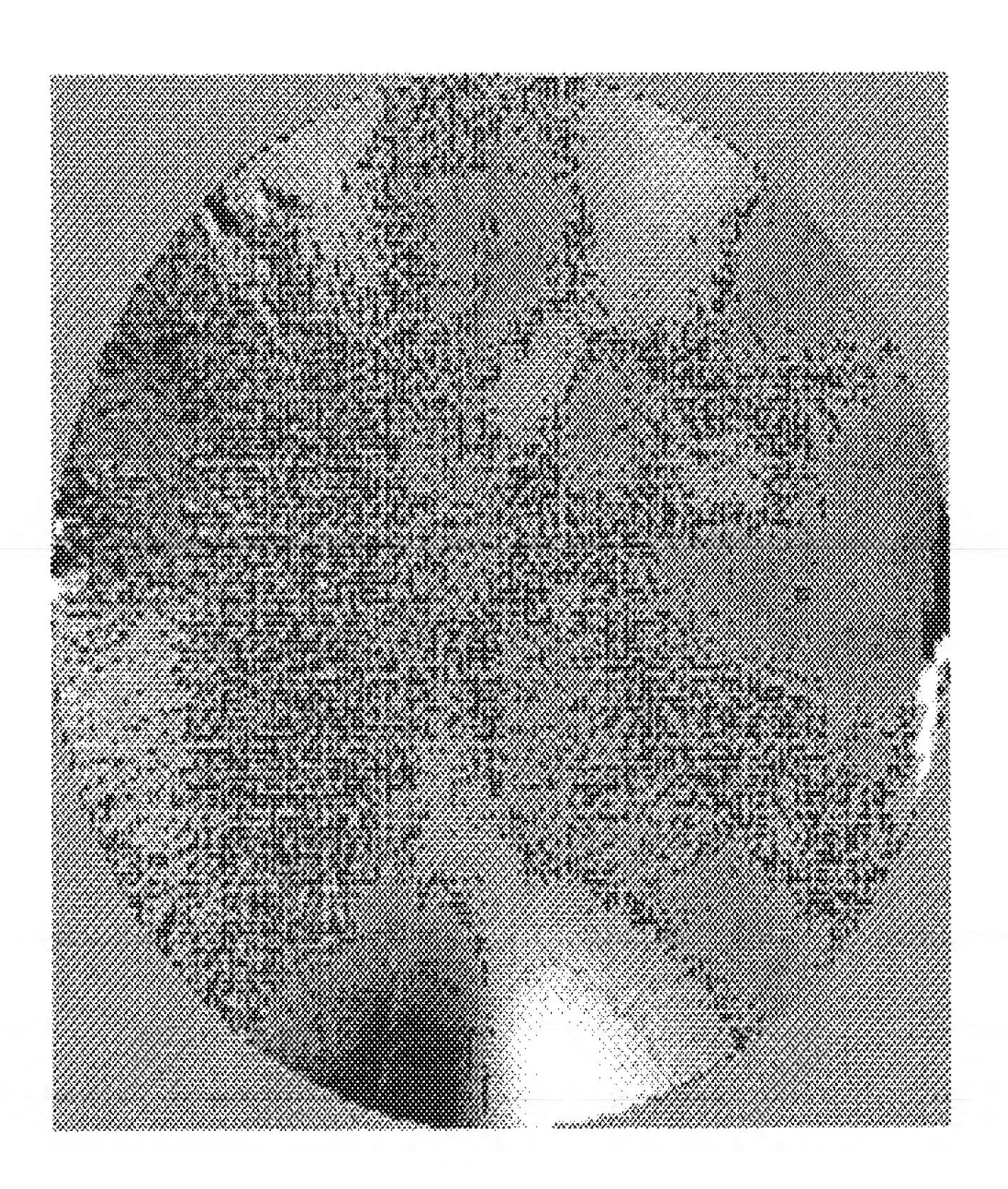
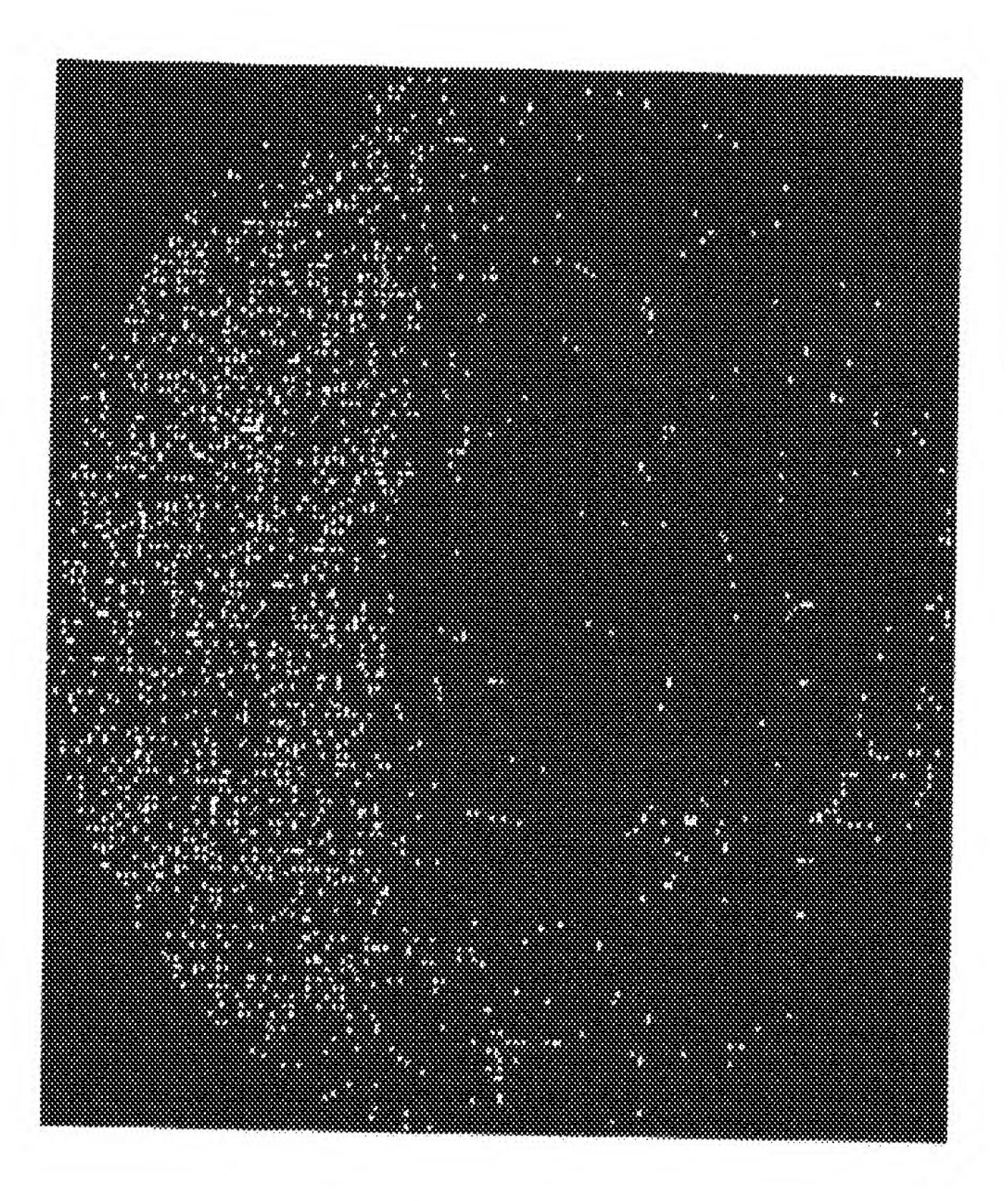


FIG. 23A



TG. 23C

